

1. INTRODUCTION

Imagination is more important than knowledge.

- A. Einstein

Esaki and Tsu[1] first proposed the concept of superlattice made from alternating layers of semiconducting materials in 1970. The original idea was to achieve negative differential resistance in a double barrier structure. Since then, a lot of theoretical as well as experimental work[2,3,4] has been devoted to the study and engineering of the semiconductor quantum heterostructures, including quantum wells, superlattices, quantum wires, quantum dots, and recently more novel nanostructures, such as carbon nanotubes.

The molecular beam epitaxy(MBE) [6] and metal-organic chemical vapor phase epitaxy (MOCVD)[7] techniques make the fabrication of high quality layered materials possible.

Lithographic techniques utilizing electron beams, focused ion beams, and x-ray have demonstrated resolution better than 20nm. Dry etching methods such as reactive ion etching and chemically assisted ion beam etching have

demonstrated similar resolutions. To a large degree, it is now possible to fabricate semiconductor structures with dimensions comparable to the De Broglie wavelength of electrons. The miniaturization and quantum size effects provide the most prominent means for creating devices faster and more efficient, more compact for more powerful integrated circuits for supercomputing and information processes.

In particular, the realization of quantum well(QW) heterostructures is of great importance to nanostructure science, in which the quantization of energy states and the formation of two dimensional electron gas lead to low threshold laser diodes and high speed modulation-doped field effect transistors(MODEFTs), respectively. For more than a decade, quantum wires (QWRs) and dots(QDs) have been a subject of both theoretical and experimental research. It has been predicted that with a further reduction in dimensionality of the carrier's motion, a quantum wire laser should exhibit threshold current densities one or two orders smaller than QW lasers, and a quantum wire MODFET will have theoretical mobilities in the $10^8 cm^2/V - s$ range[11].

To form quantum wires, the additional confinements in the lateral direction of the initial quantum wells can be achieved by patterned etching of planar structures, patterned by ion beam implantation, or growth on grooved or vicinal substrates, and more recently the strain-induced lateral ordering processes invented in 1990 in UIUC[9].

Since the late 1970s, the use of strain to modify device performance has become an important area of research. The driving force behind this development has been the gradual mastery of the art of strained hetero-epitaxy. By growing a semiconductor overlayer on top of a thick substrate, a large strain can be built into the overlayer, while still maintaining crystallinity and long-range order. In 1990, members of the MBE group at the University of Illinois at Urbana-Champaign began to study the long-range ordering properties of GaInP[8] and eventually lead to the technique of the strain-induced lateral-layer ordering process(SILO) which grows novel high quality QWRs. The fabrication of QWR's via SILO process starts with the growth of short-period superlattices (SPS) [e.g. $(\text{GaAs})_2/(\text{InAs})_{2.25}$] along the [001] direction. The excess fractional InAs layer leads to stripe-like islands during the MBE

growth[9]. The presence of stripes combined with the strain effects leads to a natural phase separation as additional layers of GaAs or InAs are deposited. A self-assembled QWR heterostructure can then be created by sandwiching the composition modulated layer between barrier materials such as $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ (quarternery), $\text{Al}_{0.48}\text{In}_{0.52}\text{As}$ (ternary), or InP (binary)[9-11]. It was found that different barrier materials can lead to different degree of lateral composition modulation, and the consequent optical properties are different [10]. The emphasis here is that the lateral quantum wells are formed in-situ during growth of the epilayers. Thus, these “wells” do not suffer from damage induced by the fabrication process. Compared to conventional techniques for fabricating quantum wires, this technique is simpler, more efficient, and damage free. Using this method, UIUC group have demonstrated that 1D strain modulation can be realized on GaAs or InP substrate using the strain-balanced multiple layer structure grown by MBE.

Besides the self-assembled lateral ordering, it is believed that the strain also plays a key role[9,10,12] in the temperature stability and optical anisotropy for the QWR laser structure. Much work has been undertaken

which predicts that by using strained-layer superlattice to form the active region of a QWR laser, the threshold current can be decreased by one order of magnitude, and the optical loss due to intervalence-band absorption and Auger recombination will also be greatly reduced[9-11]. Also, the temperature sensitivity is reduced by an order of magnitude compared with strain-free structures. Temperature sensitivity of the lasing wavelength for typical GaInAs/InP lasers is around $5 \text{ \AA}/^{\circ}\text{C}$. By using a distributed-feedback structure, the temperature dependence of the lasing wavelength can be reduced to $1 \text{ \AA}/^{\circ}\text{C}$ [9-11]. With the self-assembled GaInAs QWR, the temperature sensitivity is smaller than $0.1 \text{ \AA}/^{\circ}\text{C}$ [9,10]. Thus, it represents an important improvement on the current technology in fabricating long-wavelength lasers for fiber communication.

On the other hand, the carrier confinement resulting from the band-edge differences in heterostructures of the alternating layers lead to many novel physics, such as the highly acclaimed quantum Hall effect and the prominent structures in the optical spectrum due to excitonic effects. The properties of the layered materials differ from those three-dimensional bulk materials

in many respects. This is mostly due to the confinement of the carriers in the well region due to the differences of the band gaps of the two constituent materials. The continuous bands in a bulk material can be folded to a number of separate subbands in superlattices and further in QWRs so that a series of excitonic peaks associated with the individual electron and hole energy levels can be observed in the photo absorption and luminescence spectra. The valence bands can be changed even more drastically so that the hole effective mass for certain subbands in superlattices can be made negative for wave vector along the in-plane directions. The further confinement in QWRs system lead to further folding and more flattened valence bands in the confined direction. This change of bands along with the valence band mixing and strain-effects will lead to an enhanced optical anisotropy and many forbidden transitions in SILO wire as observed in Refs[8,9,10,11,12].

The SILO QWRs have currently attracted a lot of attention both theoretically and experimentally. The most important SILO QWRs fabricated is $Ga_xIn_{1-x}As/InP$ in UIUC which is the subject of this thesis. Recent studies indicate that the use of the strained-layer quantum wire heterostructure has

advantages of high-quality interfaces and band-gap tuning which are independent of the lattice constant of the constituent materials[9-11]. The main physics brought by the strain to the wire might be that the strain provided a microscopic way to further confine the carriers by using the strain potential. Also, the strain will provide an efficient approach to engineer the bands relative positions, such as, move the light hole bands to the edge instead of the heavy hole which will reduce the DOS substantially for the reducing of the threshold current, intervalence band absorption, and Auger rate due to the fact that the inverse order of heavy hole and light hole reduce the activation energy of effect Auger by three orders of magnitude[11]. The effect of biaxial strain on the conduction band is also important. The Γ minimum will rise in the energy with respect to the average energy of the top of the valence band by $1/3$ the rate caused by hydrostatic strain assuming the Poisson's ratio is about $1/3$. This amounts to approximately 100 meV for 4% strain. The L minima will increase by approximately half this value, i.e, 50 meV. This reduction of $\Gamma - L$ separation which is further reduced by the quantum confinement, and along with the lift of X minima degeneracy, will be beneficial

for detector system[11].

Various theoretical techniques(including effective mass, $k \cdot p$, bond-orbital, tight-binding, and pseudopotential methods) were used to calculate the electronic structures, and optical responses of semiconductor nanostructures including superlattice/quantum wells, quantum wires and quantum dots[14-16]. However, all these past studies lack of detailed consideration of the strain in the atomistic level which leads to many novel and dramatic modifications of the electronic and optical properties in nanostructures.

Even though a few theoretical studies of $\text{Ga}_x\text{In}_{1-x}\text{As}$ self-assembled QWRs based on a simplified uniform strain model have been reported[14-17]. In these calculations the SPS region is modeled by a $\text{Ga}_x\text{In}_{1-x}\text{As}$ alloy with a lateral modulation of the composition x . Although these calculations can explain the QWR band gap and optical anisotropy qualitatively, it does not take into account the detailed SPS structure and the microscopic strain distribution. The understanding of these effects is important if one wishes to have a full design capability of the self-assembled QWR optoelectronic devices. On the other hand, microscopic strain distributions in several SPS

structures have been calculated, and their electronic properties have been studied via an empirical pseudopotential method[16]. However, the effects of sandwiching the SPS structures between barrier materials so as to form QWRs have not been explored. It is worth pointing out that the effective masses obtained in the pseudopotential method for the constituent bulk materials are $0.032m_0$ and $0.092m_0$ for InAs and GaAs, respectively[16]. These values are 30% larger than the actual values ($0.024m_0$ and $0.067m_0$); thus, the energy levels of quantum confined states obtained by this method are subject to similar uncertainty.

In this thesis we present a systematic study of the effects of microscopic strain distribution on the electronic and optical properties of the $\text{Ga}_{1-x}\text{In}_x\text{As}$ self-assembled QWRs via the combination of the effective bond-orbital model (EBOM)[17] for electronic states and the valence-force-field (VFF)[19,20] model for microscopic strain distribution. Both clamped and unclamped SPS structures with different degrees of lateral alloy mixing are considered. The clamped structure has a SPS layer sandwiched between the substrate and a thick capping layer so that the interface between the top monolayer

of the SPS and the barrier region is atomically flat. The unclamped structures correspond to a SPS layer sandwiched between the substrate and a thin capping layer, which allows more flexible relaxation of interface atoms so the strain energy can be relieved. This leads to a wavy interface structure. Most self-assembled QWR samples reported to date are closer to unclamped structures with a wavy interface, although it should be possible to produce self-assembled QWRs closer to the clamped structures by using a thick capping layer.

This study shows that there are profound differences in the electronic and optical properties between the clamped and unclamped self-assembled QWR structures. In particular, we find that in clamped structures the electron and hole are confined in the Ga-rich region and the polarization of photoluminescence (PL) can go from predominantly along $[110]$ for SPS with abrupt change in In/Ga composition to predominantly along $[1\bar{1}0]$ for SPS with smooth change in In/Ga composition. On the other hand, for unclamped structures the electrons and holes are confined in the In-rich region, and the optical polarization is always predominately along $[1\bar{1}0]$ with a weak depen-

dence on the lateral alloy mixing. This implies that by changing the degree of strain relaxation at the interface between the SPS and the capping layer, one can tailor the optical properties of self-assembled QWRs. Thus, through this study, we can gain a better understanding of the strain engineering of self-assembled QWR structures which may find applications in fiber-optical communication.

We also studied the absorption spectrum of the QWRs and considered the effects of exciton on the absorptions. In bulk semiconductors, excitons are usually observable optically only in high purity samples due to rather small binding energies. However, with the advent of the heterostructure technology, the carriers, ie, electrons and holes are confined in a smaller region 1D or 2D, the interaction of electron-hole will become much stronger and the paired states have greater binding energy and stronger and sharper resonances in the optical spectra. Moreover, the energy positions, or strength, of these resonances can be controlled easily by simple electronics or optics. This ability allows one to use the excitonic transitions for high speed modulation of optical signals, as well as for optoelectronic switches, which could serve

important functions in the future information processing systems.

The theoretical study of the optical properties associated with excitonic effects can be extremely difficult for a realistic system. In addition to the structures associated with the allowed transitions described by the simple particle-in-the-box model, there are also structures associated with the forbidden transitions defined within the particle-in-the-box model, due to the mixing, folding, and strain modification of the valance band structures. There are added effects when the tunneling between the different layers are important. Furthermore, the QWRs changed the absorption spectrum drastically.

We have also studied the intersubband absorption spectrum for the purpose of IR detectors. We found the intersubbands absorption is strongly polarized along the lateral direction which gives the self-assembled quantum wires a distinct advantage over the quantum well systems for application in infra-red(IR) detection. The exciton mainly leads to an enhancement of the absorption coefficient around 1.1-1.5 times as observed[20]. Also, the lateral confinement is successfully used to engineer the intersubband spacing to get the desired absorption peak's positions for the purpose of utilizing the optimum

operating energy region for the IR detectors.

Our study on the strained heterostructure should provide a universal description to all the heterostructures in a profunded frame-work while the lattice constant matched nanostructures are special cases of our model.

In Chapter 2, we will present the theoretical models and techniques we used to study the SILO QWRs.

Chapter 3 is devoted to the study of the QWRs in a uniform continuous model using the virtual-crystal approximation (VCA) for alloys. The strain and its effects are studied in the uniform continuous frame, and the optical anisotropy observed experimentally are explained.

Chapter 4 contains our advanced technique for the investigation of the strain and its effects on the atomistic level. There, we show in details how the strain behaves in each layer and around each atom.

Chapter 5 is mainly concerned with inter-subband transitions, and inter-band transitions including the excitonic effects on the absorption spectrum. This study is important in the design of devices such as IR detectors.

A summary is presented in Chapter 6.

REFERENCES

- ¹ L. Esaki and R. Tsu, IBM J Res.Develop. **14**, 61(1970)
- ² D. L. Smith, C. Mailhoit, Reviews of Modern Physics., **62**, 173(1990)
- ³ G. Bastard, J. A. Brum and R. Ferreira in Solid State Physics Vol.**44**, 229(1991)
- ⁴ S. Schimitt-Risk, D. S. Chemla, and D.A.B. Miller, Advances in Physics.**38**, 89(1989), and references therein.
- ⁵ A.Y.Cho and J.R. Arthur, Prog. Solid State Chem.**10**, 157(1975); For the key aspects of the MBE growth, see: K. Ploog, in Excitons in Confined Systems. Springer Proceedings in Physics **25**, (Springer-verlag, Berlin, P.134.). For an extensive survey see: Proc. 4th Int. Conf. Molecular. Beam Epitaxy, J. Cryst. Growth, 811(1997)
- ⁶ For an extensive survey on MOCVD, see, Proc. 2nd Int. Conf. Metal-Organic Vapor Phase Epitaxy, J. Cryst. Growth, 77 (1986)
- ⁷ M.A. Reed and W. P. Kirk. Eds., Nanostructure Physics and Fabrication, (Academic Press, New York, 1989)

- ⁸ K. C. Hsieh, J. N. Baillargeon, and K.Y. Cheng, Appl. Phys. Lett. **57** 2244-2246(1990)
- ⁹ S.T. Chou, K. Y. Cheng, L. J. Chou, and K. C. Hsieh, Appl. Phys. Lett. **17**, 2220(1995); J. Appl. Phys. **78** 6270(1995); J. Vac. Sci. Tech. **B13**, 650(1995); K.Y. Cheng, K. C. Hsieh, and J. N. Baillargeon, Appl. Phys. Lett. **60**, 2892(1992)
- ¹⁰ D. E. Wohlert, S.T. Chou, A. C. Chen, K. Y. Cheng and K. C. Hsieh, Appl. Phys. Lett. **17**, 2386(1996)
- ¹¹ A.R. Adams, Electron. Lett. **22** , 249(1986)
- ¹² Y. Tang, H. T. Lin, D. H. Rich, P. Colter, S. M. Vernon. Phys. Rev. **B53**, R10501(1996)
- ¹³ G.D. Sanders and Y. C. Chang, Phys. Rev. **B31**, 6892(1985); **B32**, 4282(1985); **B35**, 1300(1987)
- ¹⁴ Y. Zhang, and A. Masaceranhas, Phys. Rev. **B57**, 12245(1998)
- ¹⁵ T. Mattila, L. Bellaiche, L.W. Wang, and A. Zunger, Appl. Phys. Lett. **72**, 2244(1998)

¹⁶L.W. Wang, J. Kim, and A. Zunger, Phys. Rev. **B59**, 5678(1999)

¹⁷Y. C. Chang, Phys. Rev. **B67** 8215(1988)

¹⁸P.N. Keating, Phys. Rev. **145**, 637(1966)

¹⁹R. Martin, Phys. Rev. **B1**, 4005(1969)

²⁰F. Rossi and Elisa Molinari, Phys. Rev. **B53** 16462(1996).

2. MODELING OF STRAIN AND SILO WIRES

I. STRAIN IN GENERAL.

When two lattice-mismatched materials grow on top of each other, strain is produced.

In essence, as long as the lattice mismatch is below the critical thickness, it is possible to grow an epitaxial film which is completely in registry with the substrate, i.e., it is pseudomorphic up to the critical thickness. Beyond the critical thickness, dislocation are produced and the strain relaxes. It is important to note that the pseudomorphic films below critical thickness are thermodynamically stable, i.e., even though they have strain energy, the relaxed state with dislocations has a higher free energy. This allows one to have large built-in strain without serious concern that the film will somehow “disintegrate” after some time. In this section we will establish some basic notions and formulas for strain in crystalline materials. Without losing any generality, let us consider small values of strain.

In order to define the strain quantitatively, let us consider an position vector $\vec{r}$ in a Cartesian coordinate system for an atom in the solid. There will be a small displacement $u(\vec{r})$ when a deformation force is applied on the solid, ie, the new position of the atom is at $\vec{r}' = \vec{r} + \vec{u}(r)$. The small change in length element is

$$dl'^2 = d(\vec{r} + \vec{u}(r))^2$$

and let $du_i(r) = \frac{\partial u_i(r)}{\partial x_j} dx_j$, then

$$dl'^2 = d(\vec{r} + u(\vec{r}))^2 = dl^2 + \epsilon_{ij} \cdot dx_i dx_j$$

where $\epsilon_{ij} = \frac{1}{2}(\frac{\partial u_i}{\partial x_j} + \frac{\partial u_j}{\partial x_i} + \frac{\partial u_k}{\partial x_i} \frac{\partial u_k}{\partial x_j})$ is the strain tensor. In small strain, the second order term is ignored, we have $\epsilon_{ij} = \frac{1}{2}(\frac{\partial u_i}{\partial x_j} + \frac{\partial u_j}{\partial x_i})[1]$.

For our purpose, for three arbitrary independent vectors which connect atoms 1,2,3,4 at four corners of a tetragon surrounding an atom(which is placed at the center), we set up the position matrix for the undeformed tetragon as:

$$R^0 = \begin{pmatrix} R_{12x}^0 & R_{23x}^0 & R_{34x}^0 \\ R_{12y}^0 & R_{23y}^0 & R_{34y}^0 \\ R_{12z}^0 & R_{23z}^0 & R_{34z}^0 \end{pmatrix},$$

with $\mathbf{R}_{ij}^0 = \mathbf{R}_j^0 - \mathbf{R}_i^0$; $i, j = 1, 4$ and $\mathbf{R}_i^0$ ($i = 1, 4$) denote positions of the four atoms in the system we are considering. After applying the deformation force, the new position matrix R' is related to the undeformed R^0 as

$$\vec{R}' = (1 + \epsilon) \cdot \vec{R}_0$$

with ϵ being the strain tensor defined for the center atom as

$$\epsilon = \begin{pmatrix} \epsilon_{xx} & \epsilon_{xy} & \epsilon_{xz} \\ \epsilon_{yx} & \epsilon_{yy} & \epsilon_{yz} \\ \epsilon_{zx} & \epsilon_{zy} & \epsilon_{zz} \end{pmatrix},$$

which is calculated to be[3]

$$\epsilon = R' * R_0^{-1} - 1. \quad (1)$$

This equation will be used in Chapter 4 for the calculation of strain for each atoms.

After getting the strain, the effects of the strain on band structure and optical properties are through the deformation potential given by Bir and Pikus[2]. For the effects on the valance bands, i.e, p_x, p_y , and p_z in our III-V alloys, we have[2,4]

$$H^{st} = \begin{pmatrix} -\Delta V_H + D_1 & \sqrt{3}de_{xy} & \sqrt{3}de_{xz} \\ \sqrt{3}de_{xy} & -\Delta V_H + D_2 & \sqrt{3}de_{yz} \\ \sqrt{3}de_{xz} & \sqrt{3}de_{yz} & -\Delta V_H + D_3 \end{pmatrix}, \quad (2)$$

where $e_{ij} = (\epsilon_{ij} + \epsilon_{ji})/2$, and

$$\Delta V_H = (a_1 + a_2)(\epsilon_{xx} + \epsilon_{yy} + \epsilon_{zz}), \quad D_1 = b(2\epsilon_{xx} - \epsilon_{yy} - \epsilon_{zz}),$$

$$D_2 = b(2\epsilon_{yy} - \epsilon_{xx} - \epsilon_{zz}), \quad D_3 = b(2\epsilon_{zz} - \epsilon_{yy} - \epsilon_{xx}).$$

The strain potential on the s states is given by

$$\Delta V_c = c_1(\epsilon_{xx} + \epsilon_{yy} + \epsilon_{zz}).$$

In general, tensile strain tends to narrow the gap, and push the light hole band up over the heavy hole band; compressive strain leads to the opposite results.

II. VFF MODEL OF THE GROWTH OF SILO WIRES.

The influence of the strain on the growth of the overlayers are calculated by the valence-force-field(VFF) model of Martin[5] and Keating[6]. This model has been shown to be

successful in fitting and predicting the elastic constants of elastic continuum theory, calculating strain distribution in a quantum well, and determining the atomic structure of $III-V$ alloys. It was used in the calculation of the strain distribution in self-assembled dots[7,8]. The VFF model is a microscopic theory which includes bond stretching and bond bending, and avoids the potential failure of elastic continuum theory in the atomistic thin limit. In this model, the total energy of the lattice is taken as

$$V = \frac{1}{4} \sum_{ij} \frac{3}{4} \alpha_{ij} (d_{ij}^2 - d_{0,ij}^2)^2 / d_{0,ij}^2 + \frac{1}{4} \sum_i \sum_{j \neq k} \frac{3}{4} \beta_{ijk} (\vec{d}_{ij} \cdot \vec{d}_{ik} + d_{0,ij} d_{0,ik} / 3)^2 / d_{0,ij} d_{0,ik}, \quad (3)$$

where i runs over all the atomic sites, j, k run over the nearest-neighbor sites of i , $\vec{d}_{ij}$ is the vector joining the sites i and j , d_{ij} is the length of the bond, $d_{0,ij}$ is the corresponding equilibrium length in the binary constituents, and α_{ij} and β_{ijk} are the bond stretching and bond bending constants, respectively. α and β are taken from Martin's calculations[5]. For the bond-bending parameter β of In-As-Ga, we take $\beta_{ijk} = \sqrt{\beta[ij]\beta[ik]}$ following Ref. [5,8].

To find the equilibrium atomic positions in the InAs/GaAs self-assembled QWR, we start from ideal atomic positions and minimize the system energy using the Hamiltonian given above. Minimization of the total energy requires one to solve a set of coupled equations with $3N$ variables, where N is the total number of atoms. Direct solution of these equations is impractical in our case, since the system contains more than 6,000 atoms. We use an approach taken by several authors[4,7,8] which has been shown to be quite efficient. In the beginning of the simulation all the atoms are placed on the InP lattice, we allow atoms to deviate from this starting positions and use periodic boundary conditions in the plane perpendicular to the growth direction, while keeping atoms in the planes outside the SPS region at their ideal

atomic positions for an InP lattice (since the self-assembled QWR is grown epitaxially on the InP substrate). In each iteration, only one atomic position is displaced and other atomic positions are held fixed. The direction of the displacement of atom i is determined according to the force $f_i = -\partial V/\partial x_i$ acting on it. All atoms are displaced in sequence. The whole sequence is repeated until the forces acting on all atoms become zero, at which point the system energy is a minimum. In this way, the equilibrium atomic positions are simulated.

Once the positions of all the atoms are known, the strain distribution is obtained through the strain tensor calculated according to the method described in Section 2.1.

III. EMPIRICAL BOND-ORBITAL MODEL(EBOM).

The method used in this thesis for calculating the strained quantum well band structure is based on the effective bond-orbital model (EBOM)[10]. The effective bond-orbital model employed here is a tight-binding-like model which includes nearest-neighbor interactions among bond orbital residing on an fcc lattice. The version of the EBOM used in this calculations describes the coupling between the upper four spin-3/2 valence bands and the lowest two s-like conduction bands. A bond orbital is defined to be the proper linear combination of the two atomic orbitals within a zinc-blende crystal which best describes the states near the center of the Brillouin zone. The parameters that appear in the theory are given by a correspondence which is made by requiring that the Hamiltonian in the bond-orbital basis, when written for the bulk material and expanded to the second order in $\mathbf{k}$, agree with the

Luttinger-Kohn expression. For interactions across heterojunctions, we take the arithmetic average of the matrix elements for the two bulk materials. Since the nearest-neighbor EBOM parameters for the two materials are similar, the arithmetic average is a good approximation. We have also studied the dependence of QWR energies on different choices of parameters (e.g. geometric average) and found essentially the same results[11]. EBOM has been successfully applied to the calculation of electronic states of superlattices[10], strained-layer superlattices [12,13], semiconductor quantum wires[14] and dots[15], and impurity levels in quantum dots[15] and quantum wells[15]. Here, we apply it to this multi-axially strained QWR structures.

We solve the QWR electronic states according to a procedure similar to that described in [16]. We first calculate the band structure of a superlattice(SL) with M bilayers of $Ga_xIn_{1-x}As$ (the well material) and N bilayers of $Al_{0.24}Ga_{0.24}In_{0.52}As$ (the barrier material) using the slab method. The SL eigenstates with $k_z = 0$ can be treated as eigenstates for an isolated quantum well (QW) and they are denoted by $|k_1, \bar{k}_2, n >$, i.e,

$$H^{QW}|k_1, \bar{k}_2, n > = E_n(k_1, \bar{k}_2)|k_1, \bar{k}_2, n > \quad (4)$$

where H^{QW} is the Hamiltonian for the $Ga_yIn_{1-y}As/Al_{0.24}Ga_{0.24}In_{0.52}As$ QW ,where k_1 and k_2 are the two components of the QW in-plane wave vector along and perpendicular to the QWR axis, respectively. k_1 is a good quantum number for the QWR array, while $\bar{k}_2$ is not. The QWR wave function is a linear combination of SL wave functions with the same k_1 but with values of $\bar{k}_2$ differing by $2\pi/L_2$. We define k_2 to be the wave number of the QWR array in the [110] direction, and we can write $\bar{k}_2 = k_2 + 2\pi\zeta/L_2$ with $\zeta = 0, 1, 2, \dots, m$,

where $m = L_2/a_2$ with $a_2 = a/\sqrt{2}$. The QWR Hamiltonian is $H^{QWR} = H^{SL} + H'$, where $H' = H_{Ga_xIn_{1-x}As} - H_{Ga_yIn_{1-y}As}$ is treated as a perturbation. The Hamiltonian matrix for QWR

$$M(n, \zeta | n', \zeta') = \langle n', k_1, k_2 + 2\pi\zeta'/L_2 | H^{QWR} | k_1, k_2 + 2\pi\zeta/L_2, n \rangle \quad (5)$$

is then diagonalized in the basis consisting of QW eigenstates.

The effect of lateral intermixing of Ga and In is accounted for by using the virtual-crystal approximation. Bond-orbital parameters for the inter-diffused materials are obtained by linearly interpolating between the values of the parameters for the pure materials. The optical parameters in these expressions are determined by requiring that the optical matrix elements between bulk states obtained by EBOM be identical to those obtained in the $\mathbf{k} \cdot \mathbf{p}$ theory up to second order in $\mathbf{k}$.

The effect of strain is included by adding a strain Hamiltonian H^{st} to the EBOM effective Hamiltonian[12,16,17].

REFERENCES

- ¹ L.D. Landau and E. L. Lifshitz, Theory of Elasticity (Addison-Wesley Publishing Company Inc, Reading, Massachusetts, USA, 1970).
- ² G. L. Bir and G. E. Pikus, Symmetry and Strain Induced Effects in Semiconductors (Halsted, United Kingdom, 1974);
- ³ C. Pryor, J. Kim, L.W. Wang, A.J. Williamson and A. Zunger, Phys. Rev. B**183**, 2548(1998).
- ⁴ L. X. Li and Y. C. Chang, J. Appl. Phys. **84** 6162, 1998.
- ⁵ R. Martin, Phys. Rev. B**1**, 4005(1969)
- ⁶ P.N. Keating, Phys. Rev. **145**, 637(1966)
- ⁷ H. Jiang and J. Singh, Phys. Rev. B**56**, 4696(1997).
- ⁸ O.Stier, M.Grundmann, and D.Bimberg, Phys. Rev. B **59**, 5688,(1999).
- ⁹ T. Mattila, L. Bellaiche, L. W. Wang, and A. Zunger, Appl. Phys. Lett., **72**, 2144 (1998).
- ¹⁰ Y. C. Chang, Phys. Rev. B**37**, 8215 (1988).
- ¹¹ L. Li and Y. C. Chang, unpublished.
- ¹² Mau-Phon Houng and Y.C Chang, J. Appl. Phys. **65**, 3096 (1989).
- ¹³ Mau-Phon Houng, Superlatt. Microstruct. **6**, 421 (1989).
- ¹⁴ D. S. Citrin and Y. C. Chang, Phys. Rev. B**43**, 11703 (1991).

¹⁵ G. T. Enievoll and Y. C. Chang, Phys. Rev. B**40**, 96 (1989); Phys. Rev. B**41**, 1447 (1989).

¹⁶ G. C. Osbourn, Phys. Rev. B**27**, 5126 (1983).

¹⁷ G. P. Agrawa and N. K. Dutta, Long Wavelength Semiconductor Lasers, 2nd ed. (Van. Nostrand Reinhold, New York, 1993) Chap.7.

I. INTRODUCTION

$Ga_xIn_{1-x}As$ is one of the most important ternary III-V compound semiconductors. Its bandgap covers both the 1.3 and 1.55 μm range, which are the preferred wavelengths in long distance fiber communications[1,2]. However, long-wavelength photonic devices based on lattice-matched $Ga_{0.47}In_{0.53}As$ /InP heterostructures suffer from strong Auger recombination and intervalence band absorption processes[7-10]. Recently, to improve the performance of long-wavelength semiconductor lasers, long wavelength($\sim 1.55\mu m$) $Ga_xIn_{1-x}As$ quantum-wire (QWR) lasers have been grown by a single step molecular beam epitaxy technique[1]. It is found that the QWR laser structures are a promising choice because of the many predicted benefits, such as higher gain, reduced temperature sensitivity, higher modulation bandwidths, and narrower spectral linewidths[2]. Short-period superlattices (SPS) in the direction perpendicular to the growth direction can be formed via the strain-induced lateral-layer ordering (SILO) process[1,2]. A quantum wire heterostructure can then be created by simply utilizing this SPS structure as the quantum well region in a conventional quantum heterostructure. Besides the self-assembled lateral ordering, it is believed that the strain also plays a key role[2] in the temperature stability and high anisotropy for the QWR laser structure. Recent studies indicate that the use of the strained-layer quantum wire heterostructure has advantages of high-quality interfaces and band-gap tuning which are independent of the

lattice constant of the constituent materials[3,4,6]. Furthermore, much work has been undertaken which predicts that by using strained-layer superlattice to form the active region of a quantum-wire laser, the threshold current can be decreased by one order of magnitude, and the optical loss due to intervalence-band absorption and Auger recombination will also be greatly reduced[1,2,7-11]. Also, the temperature sensitivity is reduced by an order of magnitude compared with strain-free structures[2]. A typical temperature sensitivity of the lasing wavelength is($\sim 5\text{\AA}/^{\circ}\text{C}$) for the usual GaInAs/InP lasers. By using a distributed-feedback structure, the temperature dependence of the lasing wavelength is reduced to $1\text{\AA}/^{\circ}\text{C}$ [2]. With this strained GaInAs QWR, the dependence is smaller than $0.1\text{\AA}/^{\circ}\text{C}$ [2]. It should be an important improvement on the current technology in fabricating the long wavelength lasers for fiber communication. In this chapter we study the effects of multi-axial strain on the electronic and optical properties of the QWR structures grown via the SILO process. Through this study, we can gain a better understanding of the strain engineering of QWR structures suitable for the application of fiber-optical communication.

In the experiment performed by Chou et al[1], the QWR active region is created *in situ* by the SILO process within the $(GaAs)_2/(InAs)_{2.2}$ SPS regions. The SILO process generates a strong Ga/In lateral composition modulation and creates In-rich $Ga_xIn_{1-x}As$ lateral QWs in the $[110]$ direction. By sandwiching the In composition modulated layer (with x varying from 0.3 to 0.7) between $Al_{0.24}Ga_{0.24}In_{0.52}As$ barrier layers, a strained QWR heterostructure is formed[1,2]. The model QWR structure considered in the present paper is depicted in Figure.1. The central region consists of the In composition modulated $Ga_xIn_{1-x}As$ layer

(A/B/A/B...), in which the A strip is Ga-rich while the B strip is In-rich. The lateral period is $L_2 = L_2^A + L_2^B$. In our calculation, we consider $L_2^A = L_2^B = 150\text{\AA}$, $L_\perp^B = 60\text{\AA}$, and $L_\perp^W = 100\text{\AA}$. We consider two cases of composition modulation. In case one, the Ga composition changes abruptly with $x = 0.6$ (or 0.7) in strip A and $x = 0.4$ (or 0.3) in strip B. In case two, x varies sinusoidally from 0.6 (or 0.7) at the center of strip A to 0.4 (or 0.3) at the center of strip B (with $x = 0.5$ at the border between A and B strips).

II. THEORETICAL APPROACH

The method used in this paper for calculating the strained quantum well band structure is based on the effective bond-orbital model (EBOM)[5] as described in Chapter 2. A detailed description of this method without the effect of strain has been published elsewhere[5].

The version of the EBOM used in this calculations describes the coupling between the upper four spin-3/2 valence bands and the lowest two s-like conduction bands. For our QWR system, the split-off bands are ignored since the spin-orbital splitting is large. The split-off band is about 350 meV below the valence-band maximum. The coupling energy between the heavy-hole band and split-off band via strain is about 16.47 meV in our system. Based on the second-order perturbation theory, we estimate that the inclusion of split-off band will shift the heavy-hole subbands up by approximately 0.8 meV[8]. The effects on the spacings between valence subbands should be much less, since the energy shifts are similar for the first few valence subbands.

In the diagonalization of the SILO quantum wire Hamiltonian as in Eq.2.5, the QW basis is truncated to reduce the computer time, thus making the method a variational one. The subbands closest to the band edge are converged to within 0.1 meV. The size of the Hamiltonian matrix, originally given by the number of sites in a QWR supercell times the number of coupled bands, is now reduced to the number of QW states necessary to give accurate results for the QWR of concern. In our case, this number needed to get well converged results for the two uppermost pair of valence subbands is around 200. However, we have used ~ 1200 basis states in order to ensure the accuracy of the deeper lying states for all calculations in this chapter. The effect of lateral intermixing of Ga and In is accounted for by using the virtual-crystal approximation. Bond-orbital parameters for the inter-diffused materials are obtained by linearly interpolating between the values of the parameters for the pure materials. The optical parameters in these expressions are determined by requiring that the optical matrix elements between bulk states obtained by EBOM be identical to those obtained in the $\mathbf{k} \cdot \mathbf{p}$ theory up to second order in $\mathbf{k}$ [14].

The effect of strain is included by adding a strain Hamiltonian H^{st} to the EBOM effective Hamiltonian[6,11,16]. The matrix elements of H^{st} in the bond-orbital basis can be obtained by the deformation-potential theory of Bir and Pikus[17]. Here, we consider the combination of two bi-axial strains, one in the (001) plane (due to the lattice mismatch at the interfaces between GaInAs and AlGaInAs) and the other in the (110) plane (due to the Ga composition modulation). The resulting strains in the QW layers consist of both hydrostatic and uniaxial components. For case 1 (Ga composition changes abruptly from region A to region B), the

lattice constant of the strained layers in the $[001]$ direction ($\tilde{a}_{001}$) is given by minimizing the free energy of the fcc system due to strain[8,17]

$$\begin{aligned}
F = & \frac{1}{2}C_{11}^A(\epsilon_{11A}^2 + \epsilon_{22A}^2 + \epsilon_{33A}^2)L_2^A \\
& + C_{12}^A(\epsilon_{11A}\epsilon_{22A} + \epsilon_{22A}\epsilon_{33A} + \epsilon_{11A}\epsilon_{33A})L_2^A \\
& + \frac{1}{2}C_{11}^B(\epsilon_{11B}^2 + \epsilon_{22B}^2 + \epsilon_{33B}^2)L_2^B \\
& + C_{12}^B(\epsilon_{11B}\epsilon_{22B} + \epsilon_{22B}\epsilon_{33B} + \epsilon_{11B}\epsilon_{33B})L_2^B,
\end{aligned} \tag{1}$$

where L_2^A (L_2^B) is the lateral layer thickness and ϵ_{ijA} (ϵ_{ijB}) is the strain tensor in the Ga-rich (In-rich) region. C^A 's (C^B 's) are the elastic constants for the Ga-rich (In-rich) materials. Here we have used a rotated Cartesian coordinates in which $x' = [1\bar{1}0]$, $y' = [110]$, and $z' = [001]$. A constraint $\tilde{a}_{\parallel}^A = \tilde{a}_{\parallel}^B = a_{InP} = a_{AlInGaAs}$ has been imposed to keep the $Al_{0.24}Ga_{0.24}In_{0.52}As$ barrier strain free, since it is lattice-matched to the InP substrate[1,2], where $\tilde{a}_{\parallel}^{\alpha}$ is the in-plane strained lattice constant (perpendicular to $[001]$ axis) for material α . The multi-axial strain caused by the lattice-mismatch in both (001) and (110) planes is simply

$$\epsilon_{11\alpha} = \epsilon_{22\alpha} = \frac{\tilde{a}_{\parallel}^{\alpha} - a_{\alpha}}{a_{\alpha}}, \tag{2}$$

where a_A (a_B) is the unstrained lattice constant of $Ga_xIn_{1-x}As$ ($Ga_{1-x}In_xAs$) ($x = 0.6$ for case 1) and

$$\epsilon_{33\alpha} = \frac{\tilde{a}_{001} - a_{\alpha}}{a_{\alpha}} \tag{3}$$

with $\epsilon_{ij}^{\alpha} = 0$ for $i \neq j$.

The minimization procedure leads to

$$\tilde{a}_{001} = -\frac{1}{2} \frac{C_{11}^A L_2^A / a_A^2 + C_{11}^B L_2^B / a_B^2}{(C_{12}^A \epsilon_{\parallel}^A L_2^A / a_A + C_{12}^B \epsilon_{\parallel}^B L_2^B / a_B) + (C_{11}^A L_2^A / a_A + C_{11}^B L_2^B / a_B)}, \quad (4)$$

which is the strained lattice constant in the [001] direction.

Due to symmetry, the multi-axial strain tensor is diagonal in the $x'y'z'$ coordinates, which leads to a diagonal strain Hamiltonian[8] as shown in Chapter 2:

$$H^{st} = \begin{pmatrix} -\Delta V_H + D_1 & 0 & 0 \\ 0 & -\Delta V_H + D_2 & 0 \\ 0 & 0 & -\Delta V_H + D_3 \end{pmatrix}, \quad (5)$$

where

$$\Delta V_H = (a_1 + a_2)(\epsilon_{11} + \epsilon_{22} + \epsilon_{33}), \quad D_1 = b(2\epsilon_{11} - \epsilon_{22} - \epsilon_{33}),$$

$$D_2 = b(2\epsilon_{22} - \epsilon_{11} - \epsilon_{33}), \quad D_3 = b(2\epsilon_{33} - \epsilon_{22} - \epsilon_{11})$$

The strain potential on the s states is given by[6]

$$\Delta V_c = c_1(\epsilon_{11} + \epsilon_{22} + \epsilon_{33}),$$

The strain Hamiltonian in the bond-orbital basis $|JM\rangle$ can be easily found by using the coupling constants[5], i.e,

$$\langle JM | H^{st} | J'M' \rangle = \sum_{\alpha, \alpha', \sigma} C(\alpha, \sigma; J, M)^* C(\alpha', \sigma; J', M') H_{\alpha\alpha'}^{st} \quad (6)$$

The elastic constants C_{12} and C_{11} for GaAs, InAs and AlAs can be found in Ref. [18,19]. The deformation potentials a_1 , a_2 , b , c_1 can be found in Ref.[20,21]. The linear interpolation

and virtual crystal approximation is used to obtain the corresponding parameters for the GaInAs and AlGaInAs.

The above strain Hamiltonian is derived for case one only, where the Ga composition (x) changes abruptly from region A to region B. For case two, x varies continuously from x_m to $1 - x_m$ ($x_m = 0.6$ or 0.7). In this case, we shall first calculate the strain Hamiltonian for the abrupt case to get $H_{x_m}^{st}$ and $H_{1-x_m}^{st}$, using Eq. 3.6. We then obtain the strain Hamiltonian at any atomic layer with Ga composition x via a linear interpolation between $H_{x_m}^{st}$ and $H_{1-x_m}^{st}$. This is consistent in spirit with the virtual crystal approximation we have used for obtaining the interaction parameters in EBOM.

III. RESULTS AND DISCUSSIONS

In Figure 3.2, we show a schematic diagram indicating the alignment between band edges of the constituent materials for QWR in case 1 (square profile) with and without the effect of strain[8]. All energies are measured with respect to the bulk InAs valence band edge. This diagram is useful in understanding the quantum confinement effect on the QWRs considered here. From Figure 3.2, we notice that the strain [in particular, the one in the (110) plane] has a significant effect on the band alignment. Take Figure 3.2(a) for example, without strain (solid lines) the conduction (valence) band of $\text{Ga}_{0.4}\text{In}_{0.6}\text{As}$ is below (above) that of $\text{Ga}_{0.6}\text{In}_{0.4}\text{As}$ by 202 meV (14 meV). With strain (dotted lines), the situation is reversed and the conduction (valence) band of $\text{Ga}_{0.4}\text{In}_{0.6}\text{As}$ is above (below) that of $\text{Ga}_{0.6}\text{In}_{0.4}\text{As}$ by 15

meV (94 meV); thus, both electrons and holes will be confined in the Ga-rich region of the QWR.

The strain also causes a splitting between the heavy-hole (HH) and light-hole (LH) bands with the LH band lying above the HH band. However, the splitting is rather small, about 3 meV in $\text{Ga}_{0.6}\text{In}_{0.4}\text{As}$. When the confinement effect due to the barrier material ($\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$) is included, the HH band again lies above the LH band, due to the difference in the effective masses along the growth direction (z). The dash-dotted lines in Figure 3.2(a) indicate the superlattice band edges of $100\text{\AA}\text{Ga}_{0.6}\text{In}_{0.4}\text{As}$ (or $\text{Ga}_{0.4}\text{In}_{0.6}\text{As}$) sandwiched between $60\text{\AA}\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ barriers. The difference in superlattice band edges (dash-dotted lines) between $\text{Ga}_{0.6}\text{In}_{0.4}\text{As}$ and $\text{Ga}_{0.4}\text{In}_{0.6}\text{As}$ determines the degree of lateral quantum confinement in the QWR. For the present case, the conduction-band offset is 20 meV and the valence-band (for HH only) offset is 92 meV, as far as the lateral confinement is concerned. Both offsets are large enough to give rise to lateral confinement for electrons and holes in the Ga-rich region.

Figure 3.3 shows the near zone-center valence subband structures of the $100\text{\AA}\text{Ga}_x\text{In}_{1-x}\text{As}/\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ quantum well with (a) $x = 0.6$ and (b) $x = 0.7$. The multi-axial strain on $\text{Ga}_x\text{In}_{1-x}\text{As}$ is included as if it is in the QWR geometry. All subbands are two-fold degenerate due to the Kramer's degeneracy and they are labeled according to the characters of their underlying Bloch functions at the zone-center: HH for heavy hole and LH for light-hole. The valence band structures shown here provide a useful guideline for understanding the QWR valence band structures. The black circles indicated energies at

discrete k_2 points ($k_2 = n2\pi/L_2$) which constitute the zero-th order energies for QWR at the zone center. Due to the combined effect of strain (which brings HH1 and LH1 subbands close in energy) and the band-mixing, the HH1 subband has weak dispersion for $k_2 < 0.02\text{\AA}^{-1}$. This will cause the top two valence subbands for the quantum wire to be extremely close in energy.

Figure 3.4 shows the near zone-center valence subband structures of square-shaped QWRs with the multi-axial strain with (a) Ga composition (x) changing abruptly from 0.6 in region A to 0.4 in region B and (b) Ga composition (x) changing abruptly from 0.7 in region A to 0.3 in region B. To compare with experiment[1,2], we choose material parameters appropriate for temperature at 77K[13]. Similar to the quantum well case, all subbands here are two-fold degenerate due to the Kramer's degeneracy. The conduction subbands are approximately parabolic as usual with a zone-center subband minimum equal to 845 meV in (a) and 839 meV in (b) (not shown in the figure). This gives an energy gap 847 meV for the ($x=0.6/0.4$) QWR array and 797 meV for the ($x=0.7/0.3$) QWR array .

The observed C1-HH1 excitonic transition is at 735 meV (or $1.65\mu m$) for the QWR[1,2] at 77K. In comparing the band gaps with the experiment, one should also take into account the exciton binding energy which is around 20 meV for this size of QWR. Thus, the theoretical result for the ($x=0.7/0.3$) QWR array is in closer agreement with experiment, but still about 40 meV too high.

Comparing the band structures in both k_1 ($[\bar{1}10]$) and k_2 ($[110]$) directions, we noticed an apparent anisotropy in the energy dispersion. The dispersions in the k_2 direction for the

(confined) valence bands are rather small, indicating strong lateral confinement. We observe strong anti-crossing effect between the HH1/HH2 and LH1 subband at k_1 near $0.02\text{\AA}^{-1}$ similar to what happens in a quantum well [24,25]. Here the HH2 subband of the QWR corresponds to the [110] zone-folded part of the HH1 subband of the quantum well (the envelope function has odd parity in the [110] direction but even parity in the $[1\bar{1}0]$ direction). The separation in energy between the HH1 and HH2 subbands near the zone center is extremely small (about 2 meV) in this case. This is because the HH1 subband of the quantum well has almost no dispersion (i.e. with very large effective mass) in the k_2 direction for $k_2 < 0.02\text{\AA}^{-1}$ as a result the HH1-LH1 band mixing (see Figure 3.3).

The subbands in Figure 3.4(b) have less dispersion in the k_2 direction compared with those in Figure 3.4(a) as a result of stronger lateral confinement. This is caused by the larger band discontinuities in the $x=0.3/0.7$ case (versus the $x=0.4/0.6$ case) as can be seen by comparing band alignments shown in Figure 3.2.

Figure 3.5 shows the near zone-center valence subband structures of a QWR with a sinusoidal lateral modulation with Ga composition (x) varying as the position (y') in the [110] direction between two extreme values x_m and $1 - x_m$, i.e.

$$x(y') = 0.5 + (0.5 - x_m)\sin(2\pi y'/L_2)$$

for $x_m = 0.4$ and (b) $x_m = 0.3$. In this case, the Hamiltonian including the multi-axial strain is calculated with a linear extropolation between the Hamiltonians for the maximum and minimum Ga composition, i.e.

$$H_{Ga_x In_{1-x} As}^{st} = f H_{Ga_{x_m} In_{1-x_m} As} + (1 - f) H_{Ga_{1-x_m} In_{x_m} As},$$

where $x_m = 0.4$ or 0.3 and f is determined by comparing the Ga composition on both sides of the equation

$$x = x_m f + (1 - x_m)(1 - f),$$

or $f = (1 - x_m - x)/(1 - 2x_m)$.

The conduction band minimum (not shown) is 846 meV (842 meV) for the case $x_m = 0.4$ ($x_m = 0.3$), which corresponds to a band gap of 853 meV (807 meV). Subtracting the exciton binding energy (~ 20 meV) from the band gap, we found that the $x_m = 0.3$ case is in closer agreement with the observed excitonic transition energy of 735 meV. The band gaps of QWR's with the sinusoidal profile are consistently larger (by about 10 meV) than the corresponding QWR's with the square-profile (with the same extreme values of Ga composition). The sinusoidal variation in Ga composition gives rise to more energy, since the well region contains more materials with band gap higher than the minimum in comparison with the square-profile. Furthermore, the lateral strain is reduced (less mismatch on the average) which also tend to increase the band gap.

Comparing Figure 3.5 with Figure 3.4, we notice that the spacing between HH1 and HH2 is substantially larger for the sinusoidal profile than for the square profile. This can be understood by the following argument. The envelope function for the HH2 state is more spread out than that for the HH1 state, thus its energy is increased more in the sinusoidal profile (with higher probability being in materials with higher band gap) compared with the square profile.

Next we discuss the optical properties of QWR's. Since the QWR states can be qual-

itatively viewed as the zone-folded states of the quantum well (QW) states (the zeroth-order states) via the lateral confinement, it is instructive to examine the optical matrix elements of the QW case. Figure 3.6 shows the squared optical matrix elements of the $100\text{\AA}\text{Ga}_{0.7}\text{In}_{0.3}\text{As}/\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ quantum well for the HH1-C1 and LH1-C1 transitions versus the wave vector k_2 . The solid and dashed lines are for the polarization vector along the k_1 ($[1\bar{1}0]$) and k_2 ($[110]$) directions, respectively. We note that the optical matrix elements are isotropic in the x - y plane at the zone-center, while they become anisotropic at finite values of k_2 . At the zone center, the HH state consists of Bloch states with atomic character $(x' + iy') \uparrow$ ($|J, M \rangle = |3/2, 3/2 \rangle$), while the LH state consists of Bloch states with atomic character $(x' - iy') \uparrow + 2z \downarrow$ ($|J, M \rangle = |3/2, -1/2 \rangle$); thus, the corresponding optical transitions (to an s-like conduction band state) are isotropic in the x - y plane. Here $x'(y')$ is the coordinate along the $k_1(k_2)$ direction. For finite k_2 , the HH and LH characters are mixed, with the HH state consisting of more x' -character than y' -character, thus in favor of the polarization vector parallel to the k_1 direction. Note that the HH (LH) band tends to have an atomic character with polarization perpendicular (parallel) to the direction of wave vector. This is a direct consequence of the fact that the $(pp\pi)$ interaction is weaker than the $(pp\sigma)$ interaction in a tight-binding model. Since QWR states are derived from the QW states with finite values of k_2 , we expect the optical matrix elements of QWR to be anisotropic in the x - y plane as well.

Figures 3.7 and 3.8 show the squared optical matrix elements versus wave vectors of the corresponding QWR's considered in Figures 3.4 and 3.5, respectively. The solid

and dashed lines are for the polarization vector along the k_1 ($[1\bar{1}0]$) (parallel to the wire) and k_2 ($[110]$) (perpendicular to the wire) directions. The optical matrix elements together with the subband structures discussed above provide the essential ingredients for understanding the optical transitions observed in the photoluminescence (PL) measurements. In these figures the optical transitions considered are from the topmost three valence subbands to the lowest conduction subband: HH1-C1, HH2-C1, and LH1-C1. These curves were obtained by summing the contributions of two degenerate subbands (due to Kramer's degeneracy) for the initial and final states. To compare with experimental (PL) results, we concentrate on the HH1-C1 transition.

From Figures 3.7 and 3.8, we found for the parallel polarization (solid lines), the squared optical matrix element for the HH1-C1 transition has a maximum at the zone center with a value near 10 eV and remains close to this value for all finite k_2 and with $k_1 = 0$. For the perpendicular polarization, the HH1-C1 transition is very small for finite k_2 and $k_1 = 0$. This means that the wave function of the HH1 state has mostly x' character (and some z character). Thus, we conclude that the strong lateral confinement forces the wave function of the HH1 state with $k_1 = 0$ to change from the $x' + iy'$ character (in the QW case) into mostly x' character. At finite k_1 , the character of the HH1 state gradually changes back toward the $x' + iy'$ character and the optical transition becomes almost isotropic when k_1 is comparable to zone-boundary value of $k_2(\pi/L_2)$, and finally turns into mostly y' character as k_1 becomes much larger than (π/L_2) . The anti-crossing behavior of the HH1/HH2 subbands with the LH1 subband further complicates the whole picture at $k_1 \approx 2\text{\AA}^{-1}$.

The HH2-C1 transition has zero optical strength at the zone center for both polarizations. This is expected, since the HH2 state has odd parity in the envelope function, which leads to forbidden transition at the zone center. The symmetry restriction is relaxed as the wave vector deviate from zero. The LH1-C1 transition has large optical strength (around 17 eV) for the perpendicular polarization and weak strength (around 4 eV) for the parallel polarization at the zone center. This indicates that the LH1 states consists of mostly y' character. So the strong lateral confinement forces the the wave function of the LH1 state with $k_1 = 0$ to change from the $x' - iy'$ character (in the QW case) into mostly y' character. In other words, the HH1 state (with pure $x' + iy'$ character) and LH1 state (with pure $x' - iy'$ character) in the QW case are mixed thoroughly by the lateral confinement in QWR to produce a predominantly x' state (HH1) and a predominantly y' (LH1) state. Note that all these states consist of appreciable z character, which will appear in the optical transition with z polarization.

To calculate the anisotropy, we integrate the squared optical matrix element over range of k_1 corresponding to the spread of exciton envelope function in the k_1 space and average over two k_2 points. Because the lateral confinement for the quantum wire is strong, the optical anisotropy was found to be rather insensitive to the variation in k_2 . Thus, the two point average in k_2 space is adequate. The exciton envelope function is obtained by solving the 1D Schrödinger equation for the exciton in the effective-mass approximation

$$\left[-\frac{\hbar^2}{2\mu}\left(\frac{\partial}{\partial x'}\right)^2 + V_X(x')\right]F(x') = E_X F(x'), \quad (7)$$

where μ is the exciton reduced mass ($\approx 0.049m_0$) and $V_X(x')$ is the effective 1D exciton

potential given by[24]

$$V_X(x') = \frac{e^2}{\epsilon_0|x'|}(1 - e^{-\beta|x'|}).$$

The parameter β is obtained by extrapolation from the values given in Table V of Ref. 25. For a 150Å quantum wire, we obtain $\beta = 0.03\text{\AA}^{-1}$. Eq. (10) is solved numerically, and the exciton envelope function in k_1 space is obtained via the Fourier transform of $F(x')$. The exciton binding energy obtained is 17 meV. We found that the ratio of the averaged optical strength for the HH1-C1 transition for the parallel to perpendicular component of the polarization vector is 3.41 (5.48) for the $x = 0.4/0.6$ ($x = 0.3/0.7$) QWR with square profile, and 5.60 (12.3) for the $x_m = 0.4$ ($x_m = 0.3$) QWR with sinusoidal profile. The $x_m = 0.3$ case shows stronger optical anisotropy than the $x_m = 0.4$ case, indicating that the stronger lateral confinement leads to stronger optical anisotropy as expected. Experimentally, the optical anisotropy is found to be around 2-4. So, our results are consistent with experiment.

IV. CONCLUSION

We have calculated the band structures and optical matrix elements for the strained QWR grown by the SILO method. The effect of multi-axial strain on the valence subbands and optical matrix elements is discussed. Our theoretical studies provide the explanation of the anisotropy in optical matrix elements of these QWR's observed experimentally. We find that the biaxial strain due to the lattice mismatch between the Ga-rich and In-rich regions is most dominant. It tends to increase the lateral confinement in the QWR and enhances the

anisotropy of the optical transitions which may be useful for certain applications in optical communication. We also calculated the effect of lateral composition modulation on the band structures and optical properties and find that it increases the band gaps and the optical anisotropy.

REFERENCES

- ¹ S.T. Chou, K. Y. Cheng, L. J. Chou, and K. C. Hsieh, Appl. Phys. Lett. **17**, 2220 (1995); J. Appl. Phys. **78** 6270, (1995); J. Vac. Sci. Tech. B **13**, 650 (1995); K. Y. Cheng, K. C. Hsien, and J. N. Baillargeon, Appl. Phys. Lett. **60**, 2892 (1992).
- ² D. E. Wohlert, S. T. Chou, A. C Chen, K. Y. Cheng, and K. C. Hsieh, Appl. Phys. Lett. **17**, 2386 (1996).
- ³ J. W. Matthews and A. E. Blakeslee, J. Cryst. Growth **27**, 118 (1974).
- ⁴ G. C. Osbourn, Phys. Rev. B**27**, 5126 (1983).
- ⁵ Y. C. Chang, Phys. Rev. B**37**, 8215 (1988).
- ⁶ Mau-Phon Houng and Y.C Chang, J. Appl. Phys. **65**, 3096 (1989).
- ⁷ P. L. Gourley, J. P. Hohimer, and R. M. Biefeld, Appl. Phys. Lett. **47**, 552 (1985).
- ⁸ Liang-Xin Li and Y. C. Chang, J. Appl. Phys.**84**, 6162(1998).
- ⁹ A. R. Adams, Electron. Lett. **22**, 249 (1986).
- ¹⁰ E. Yablonovitch and E. O. Kane. IEEE J. Lightwave Technol. LT-4, 504 (1986).
- ¹¹ G. P. Agrawa and N. K. Dutta, Long Wavelength Semiconductor Lasers, 2nd ed. (Van. Nostrand Reinhold, New York, 1993) Chap.7.
- ¹² L. Li and Y. C. Chang, unpublished.
- ¹³ Mau-Phon Houng, Superlatt. Microstruct. **6**, 421 (1989).

- ¹⁴ D. S. Citrin and Y. C. Chang, Phys. Rev. B**43**, 11703 (1991).
- ¹⁵ G. T. Enievoll and Y. C. Chang, Phys. Rev. B**40**, 9683 (1989); Phys. Rev. B**41**, 1447 (1989).
- ¹⁶ G. C. Osbourn, J. Appl. Phys. **53**, 1586 (1981).
- ¹⁷ G. L. Bir and G. E. Pikus, Symmetry and Strain Induced Effects in Semiconductors (Halsted, United Kingdom, 1974); L.D. Landau and E. L. Lifshitz, Theory of Elasticity (Addison-Wesley Publishing Company Inc, Reading, Massachusetts, USA, 1970).
- ¹⁸ S. Adachi, J. Appl. Phys. **53**, 8775 (1982).
- ¹⁹ H. Mathieu, P. Meroe, E. L. Amerziane, B. Archilla, J. Camassel, and G. Poiblaud, Phys. Rev. B**19**, 2209 (1979); S. Adachi and C. Hamaguchi, Phys. Rev. B**19**, 938 (1979).
- ²⁰ J. M. Hinckley and J. Singh, Phys. Rev. B**42**, 3546 (1990).
- ²¹ O. Madelung and M. Schulz, Landolt-Borstein (1982).
- ²² S. L. Chuang, Table III in Appendix.K, Physics of Optoelectronics Devices(John Wiley & Sons, Inc, 1995)
- ²³ C. G. Vande Walle, Phys. Rev. B**39**, 1871 (1989).
- ²⁴ G. D. Sanders and Y. C. Chang, Phys. Rev. B **31**, 6892 (1985).
- ²⁵ G. D. Sanders and Y. C. Chang, Phys. Rev. B**45**, 9202 (1992).

FIGURES

FIG. 1. Schematic sketch of the QWR array fabricated in Refs. [1,2]. The QWR axis lies in the $[1\bar{1}0]$ direction. A and B label the Ga-rich and In-rich strips, respectively.

FIG. 2. Schematic diagram indicating the alignment between band edges of the constituent materials for QWR in case 1 (square profile) with and without the effect of strain. Solid lines are for unstrained bulk, dotted lines are for bulk under multi-axial strain appropriate for the present QWR, and dash-dotted lines are for a 100ÅGaInAs/AlGaInAs quantum well including the multi-axial strain.

FIG. 3. Valance sub-band structures for the $100\text{\AA}\text{Ga}_x\text{In}_{1-x}\text{As}/\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ quantum well with (a) $x = 0.6$ and (b) $x = 0.7$.

FIG. 4. Valance subband structures for QWR's with square profile for (a) Ga-composition $x = 0.6$ in Ga-rich and $x = 0.4$ in In-rich region and (b) $x = 0.7$ in Ga-rich and $x = 0.3$ in In-rich region.

FIG. 5. Valance subband structures for QWR's with sinusoidal profile with x ranging from x_m to $1 - x_m$ for (a) $x_m = 0.6$ and (b) $x_m = 0.7$.

FIG. 6. Squared optical matrix elements for transitions from HH1 and LH1 to the first conduction subband of the $100\text{\AA}\text{Ga}_{0.7}\text{In}_{0.3}\text{As}/\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ quantum well for light polarized parallel (solid), perpendicular (dashed) to the QWR axis and z component (dash-dotted).

FIG. 7. Squared optical matrix elements for transitions from the top three valence subbands to the first conduction subband for light polarized parallel (solid) and perpendicular (dashed) to the QWR axis for QWR's considered in Fig. 3.3.

FIG. 8. Squared optical matrix elements for transitions from the top three valence subbands to the first conduction subband for light polarized parallel (solid) and perpendicular (dashed) to the QWR axis for QWR's considered in Fig. 3.4.

I. INTRODUCTION

Optical properties of III-V semiconductor nanostructures have attracted a great deal of interest recently for their applications in optical communications that involve switching, amplification, and signal processing.

The fabrication of QWR's via the strain-induced lateral-layer ordering (SILO) process starts with the growth of short-period superlattices (SPS) [e.g. $(\text{GaAs})_2/(\text{InAs})_{2.25}$] along the $[001]$ direction. The excess fractional InAs layer leads to stripe-like islands during the MBE growth.[4] The presence of stripes combined with the strain effect lead to a natural phase separation as additional layers of GaAs or InAs are deposited. A self-assembled QWR heterostructure can then be created by sandwiching the composition modulated layer between barrier materials such as $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ (quaternary), $\text{Al}_{0.48}\text{In}_{0.52}\text{As}$ (ternary), or InP (binary)[4-6]. It was found that different barrier materials can lead to different degree of lateral composition

modulation, and the consequent optical properties are different.[6] Besides the self-assembled lateral ordering, it is believed that the strain also plays a key role[5,6] in the temperature stability and optical anisotropy for the QWR laser structure.

Our theoretical study of $\text{Ga}_x\text{In}_{1-x}\text{As}$ self-assembled QWRs in Chapter 3 is based on a simplified uniform strain model as used in few other studies[8-10]. In these calculations, the SPS region is modeled by a $\text{Ga}_x\text{In}_{1-x}\text{As}$ alloy with a lateral modulation of the composition x . Although these calculations can explain the QWR band gap and optical anisotropy qualitatively, it does not take into account the detailed SPS structure and the microscopic strain distribution. The understanding of these effects is important if one wishes to have a full design capability of the self-assembled QWR optoelectronic devices. On the other hand, microscopic strain distributions in several SPS structures have been calculated, and their electronic properties have been studied via an empirical pseudopotential method[11]. However, the effects of sandwiching the SPS structures between barrier materials so as to form QWRs have not been explored. It is worth pointing out that the effective

masses obtained in the pseudopotential method for the constituent bulk materials are $0.032m_0$ and $0.092m_0$ for InAs and GaAs, respectively.[12] These values are 30% larger than the actual values ($0.024m_0$ and $0.067m_0$); thus, the energy levels of quantum confined states obtained by this method are subject to similar uncertainty.

In this chapter, we present a systematic study of the effects of microscopic strain distribution[11] on the electronic and optical properties of the $\text{Ga}_{1-x}\text{In}_x\text{As}$ self-assembled QWRs via the combination of the effective bond-orbital model (EBOM) for electronic states and the valence-force-field (VFF) model for microscopic strain distribution. Both clamped and unclamped SPS structures with different degrees of lateral alloy mixing are considered. The clamped structure has a SPS layer sandwiched between the substrate and a thick capping layer so that the interface between the top monolayer of the SPS and the barrier region is atomically flat. The unclamped structures correspond to a SPS layer sandwiched between the substrate and a thin capping layer, which allows more flexible relaxation of interface atoms so the strain energy can be relieved. This leads to a wavy interface structure. Most

self-assembled QWR samples reported to date are closer to unclamped structures with a wavy interface, although it should be possible to produce self-assembled QWRs closer to the clamped structures by using a thick capping layer.

This study shows that there are profound differences in the electronic and optical properties between the clamped and unclamped self-assembled QWR structures. In particular, we find that in clamped structures the electron and hole are confined in the Ga-rich region and the polarization of photoluminescence (PL) can go from predominantly along $[110]$ for SPS with abrupt change in In/Ga composition to predominantly along $[1\bar{1}0]$ for SPS with smooth change in In/Ga composition. On the other hand, for unclamped structures the electrons and holes are confined in the In-rich region, and the optical polarization is always predominately along $[1\bar{1}0]$ with a weak dependence on the lateral alloy mixing. This implies that by changing the degree of strain relaxation at the interface between the SPS and the capping layer, one can tailor the optical properties of self-assembled QWRs. Thus, through this study, we can gain a better understanding of the strain engineering of

self-assembled QWR structures which may find applications in fiber-optical communication.

II. MODEL STRUCTURES

For both clamped and unclamped SPS structures, we consider varying degrees of lateral alloy mixing and examine the effects of the microscopic strain distribution on the electronic and optical properties. Two example QWR model structures considered in the present paper (prior to alloy mixing) are depicted in Figure 4.1. The supercell of the first model structure consists of 8 pairs of (001) $(\text{GaAs})_2/(\text{InAs})_2$ SPS with a total thickness of $\approx 94 \text{ \AA}$ (quantum well region) followed by a $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ layer (barrier region) with thickness $\approx 60 \text{ \AA}$ (20 diatomic layers). The supercell of the second model structure consists of 8 pairs of (001) $(\text{GaAs})_2/(\text{InAs})_{2.25}$ SPS with a total thickness of $\approx 106 \text{ \AA}$ (quantum well region) followed by a $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ layer (barrier region). We assume an arrangement of alternating stripe like islands due to strain induced lateral ordering. In the diagram, no lateral alloy mixing is shown. In our calculations of strain dis-

tribution and electronic structures, varying degree of lateral alloy mixing will be considered. Experimentally, self-assembled InGaAs QWRs were usually grown with the (2/2.25) SPS structure.[6] However, the migration of excess In atoms during MBE growth could lead to a structure somewhere between (2/2) SPS and (2/2.25) SPS structures.

In both model structures, we can divide the self-assembled QWR into two regions with the left half being Ga rich and the right half In rich. During growth, varying degree of lateral alloy mixing of these islands with the surrounding atoms is likely to occur. In the atomic layers with In-rich alloy filled the right half of the unit cell (layer 2 in structure 1 and layers 7 and 9 in structure 2), the In composition x_{In} is assumed to vary in the $[110]$ direction (or y' direction) according to the relation

$$x_{\text{In}} = \begin{cases} x_m[1 - \sin(\pi y'/2b)]/2 & \text{for } y' < b \\ 0 & \text{for } b < y' < L/2 - b \\ x_m\{1 + \sin[\pi(y' - L/2)/2b]\}/2 & \text{for } L/2 - b < y' < L/2 + b \\ x_m & \text{for } L/2 + b < y' < L - b \\ x_m\{1 - \sin[\pi(y' - L)/2b]\}/2 & \text{for } y' > L - b, \end{cases} \quad (1)$$

where x_m is the maximum In composition in the layer, $2b$ denotes the width

of lateral composition grading, and L is the period of the lateral modulation in the $[110]$ direction. In layer 4 of structure 1, which contains Ga-rich alloy in the left half of the unit cell, the Ga composition (x_{Ga}) as a function of y' is given by a similar equation with the sign of the sine function reversed as compared to Eq. 4.1. In structure 2, there are a few atomic layers that contain 0.25 monolayer of In (layers 3 and 13) or Ga (layers 5 and 11). The lateral alloy modulation in layers 3 and 13 is described by

$$x_{\text{In}} = \begin{cases} 0 & \text{for } 0 < y' < 5L/8 - b \\ x_m \{1 + \sin[\pi(y' - 5L/8)/2b]\}/2 & \text{for } 5L/8 - b < y' < 5L/8 + b, \\ x_m & \text{for } 5L/8 + b < y' < 7L/8 - b \\ x_m \{1 - \sin[\pi(y' - 7L/8)/2b]\}/2 & \text{for } 7L/8 - b < y' < 7L/8 + b \\ 0 & \text{for } 7L/8 + b < y' < L. \end{cases} \quad (2)$$

Similar equation for x_{Ga} in layers 5 and 11 can be deduced from the above.

By varying the parameters x_m and b , we can get different degrees of lateral alloy mixing. Typically x_m is between 0.6 and 1, and b is between zero and $15a_{[110]} \approx 62 \text{ \AA}$.

A VFF model[13-15] is used to find the equilibrium atomic positions in the self-assembled QWR structure by minimizing the lattice energy. The strain

tensor at each atomic (In or Ga) site is then obtained by calculating the local distortion of chemical bonds. We find that different local arrangement of atoms can lead to very different strain distribution. In particular, the shear strain in the clamped structure can change substantially when the In/Ga composition modulation is changed. Consequently, the optical anisotropy can be reversed due to the change in the strength of the shear strain caused by the intermixing of In and Ga atoms.

III. THEORETICAL APPROACH

The method used in this paper for calculating the strained QWR band structure is based on EBOM[5] as described in Chapter 2. The model can be viewed as a spatially discretized version of the $\mathbf{k} \cdot \mathbf{p}$ method, while retaining the virtues of LCAO (linear combination of atomic orbitals) method. The $\mathbf{k} \cdot \mathbf{p}$ model is the most popular one for treating electronic structures of semiconductor quantum wells or superlattices. However, when applied to complex structures such as self-assembled quantum wires[4-9] or quantum

dots[13,18,19], the method becomes very cumbersome if one wishes to implement the correct boundary conditions that take into account the differences in $\mathbf{k} \cdot \mathbf{p}$ band parameters for different materials involved. EBOM is free of this problem, since different material parameters are used at different atomic sites in a natural way. For simple structures, when both EBOM and $\mathbf{k} \cdot \mathbf{p}$ model are equally applicable, the results obtained are essentially identical.[16]

The optical matrix elements for the QWR states are computed in terms of elementary optical matrix elements between the valence-band bond orbitals and the conduction-band orbitals. The present calculation includes the coupling of the top four valence bands and the lowest two conduction bands (including spin degeneracy). Thus, it is equivalent to a 6-band $\mathbf{k} \cdot \mathbf{p}$ model. For our systems studied here, the band-edge properties are relatively unaffected by the split-off band due to the large spin-orbit splitting as discussed in our previous paper[9]. Hence, the split-off bands are ignored here. The bond-orbitals for the GaAs and InAs needed in the expansion of the superlattice states contain the following: four valence-band bond orbitals per bulk unit cell, which are p-like orbitals coupled with the spin to form orbitals with

total angular momentum $J=3/2$ plus the products of the s-like conduction-band bond orbital and the electron spinors. The valence-band bond-orbitals are written as

$$|\mathbf{R}, u_{JM} \rangle = \sum_{\alpha, \sigma} C(\alpha, \sigma, J, M) |\mathbf{R}, \alpha \rangle \chi_{\sigma}, \quad (3)$$

where $J = 3/2$, $M = -3/2, \dots, 3/2$, χ_{σ} designates the electron spinor ($\sigma=1/2, -1/2$), and $|\mathbf{R}, \alpha \rangle$ denotes an α -like ($\alpha = x, y, z$) bond orbital located at unit cell $\mathbf{R}$. $C(\alpha, \sigma, J, M)$ are the coupling coefficients obtainable by group theory. All these bond orbitals are assumed to be sufficiently localized so that the interaction between orbitals separated farther than the nearest-neighbor distance can be ignored.

The effect of strain is included by adding a strain Hamiltonian H^{st} to the EBOM Hamiltonian[17]. The matrix elements of H^{st} in the bond-orbital basis can be obtained by the deformation-potential theory of Bir and Pikus[20]. We use the VFF model of Keating[14] and Martin[15] to calculate the microscopic strain distribution as described in Chapter 2.

To find the strain tensor in the InAs/GaAs self-assembled QWR, we start from ideal atomic positions and minimize the system energy using the Hamil-

tonian given above. Minimization of the total energy requires one to solve a set of coupled equations with $3N$ variables, where N is the total number of atoms. Direct solution of these equations is impractical in our case, since the system contains more than 6,000 atoms. We use an approach taken by several authors[10,13,19] which has been shown to be quite efficient. In the beginning of the simulation all the atoms are placed on the InP lattice, we allow atoms to deviate from this starting positions and use periodic boundary conditions in the plane perpendicular to the growth direction, while keeping atoms in the planes outside the SPS region at their ideal atomic positions for an InP lattice (since the self-assembled QWR is grown epitaxially on the InP substrate). In each iteration, only one atomic position is displaced and other atomic positions are held fixed. The direction of the displacement of atom i is determined according to the force $f_i = -\partial V/\partial x_i$ acting on it. All atoms are displaced in sequence. The whole sequence is repeated until the forces acting on all atoms become zero, at which point the system energy is a minimum. Once the positions of all the atoms are known, the strain distribution is obtained through the strain tensor calculated according to the

method described in Equation 2.5 [21] as described in Chapter 2.

Once the strain tensor is obtained, the strain Hamiltonian is given by Bir and Pikus[20]

$$H^{st} = \begin{pmatrix} -\Delta V_H + D_1 & \sqrt{3}de_{xy} & \sqrt{3}de_{xz} \\ \sqrt{3}de_{xy} & -\Delta V_H + D_2 & \sqrt{3}de_{yz} \\ \sqrt{3}de_{xz} & \sqrt{3}de_{yz} & -\Delta V_H + D_3 \end{pmatrix}, \quad (4)$$

where $e_{ij} = (\epsilon_{ij} + \epsilon_{ji})/2$, and

$$\Delta V_H = (a_1 + a_2)(\epsilon_{xx} + \epsilon_{yy} + \epsilon_{zz}), \quad D_1 = b(2\epsilon_{xx} - \epsilon_{yy} - \epsilon_{zz}),$$

$$D_2 = b(2\epsilon_{yy} - \epsilon_{xx} - \epsilon_{zz}), \quad D_3 = b(2\epsilon_{zz} - \epsilon_{yy} - \epsilon_{xx}).$$

The strain potential on the s states is given by

$$\Delta V_c = c_1(\epsilon_{xx} + \epsilon_{yy} + \epsilon_{zz}),$$

The strain Hamiltonian in the bond-orbital basis $|JM\rangle$ can be easily found by using the coupling constants[13], i.e,

$$\langle JM|H^{st}|J'M'\rangle = \sum_{\alpha,\alpha',\sigma} C(\alpha,\sigma;J,M)^* C(\alpha',\sigma;J',M') H_{\alpha\alpha'}^{st} \quad (5)$$

The elastic constants C_{12} and C_{11} for GaAs, InAs and AlAs can be found in Refs. [22,23]. The deformation potentials a_1 , a_2 , b , c_1 , d can be found

in Refs. [23-26]. The linear interpolation and virtual crystal approximations are used to obtain the corresponding parameters for the barrier material ($\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$).

The above strain Hamiltonian is derived locally for the each cation atom in the self-assembled QWR considered. To calculate the electronic states of the self-assembled QWR for model structure 1 [Fig.4.1(a)], we first construct a *zeroth*-order Hamiltonian for a superlattice structure which contains in each period 8 pairs of (001) $(\text{GaAs})_2/(\text{InAs})_2$ SPS layers (with a total thickness around 94 Å) and 20 diatomic layers of $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ (with thickness around 60 Å). So, the superlattice unit cell for the *zeroth*-order model contains 52 diatomic layers. The appropriate strain Hamiltonian for the $(\text{GaAs})_2/(\text{InAs})_2$ SPS on InP is also included. For model structure 2 [Fig. 4.1(b)], the *zeroth*-order superlattice consists of two additional monolayers of InAs inserted into the 8 pairs of (2/2) SPS: one between the 2nd and 3rd pair of (2/2) SPS, the other between the 5th and 6th pair of (2/2) SPS.

The eigen-states for the *zeroth*-order Hamiltonian for different values of k_2 (separated by the SL reciprocal lattice vectors in the [110] direction) are then

used as the basis for calculating the self-assembled QWR electronic states. The difference in the Hamiltonian (including strain effects) caused by the intermixing of Ga and In atoms at the interfaces is then added to the *zeroth*-order Hamiltonian, and the electronic states of the full Hamiltonian is solved by diagonalizing the Hamiltonian matrix defined within a truncated set of eigen-states of the *zeroth*-order Hamiltonian. A total of ~ 500 eigen-states of the *zeroth*-order Hamiltonian (with 21 different k_{110} points) were used in the expansion. The subbands closest to the band edge are converged to within 0.1 meV.

IV. RESULTS AND DISCUSSIONS

A. Strain distributions

In this section we discuss strain distributions in our model structures as described in Sec. 4.2. Both clamped and unclamped situations are considered. To model the alloy structure with composition modulation, we use a super-cell which contains 72 atoms in the $[110]$ (y') direction, 36 atoms in the $[1\bar{1}0]$ (x') direction and 64 or 68 atomic planes along the $[001]$ (z) direction [8 pairs of (2/2) or (2/2.25) SPS] plus a GaAs capping layer. In the atomic planes

which consist of alloy structure, we first determine the In composition at a given y' according to either Eq. 4.1 or 4.2 and then use a random number generator to determine the atomic species along the x' direction. The bottom layer of atoms are bonded to the InP substrate with the substrate atoms fixed at their ideal atomic positions. The calculated strain distributions are then averaged over the x' coordinate. For the clamped case, the GaAs capping layer is assumed to be lattice matched to InP with a flat surface. For the unclamped case, the capping layer is allowed to relax freely, thus giving rise to a wavy surface structure.

The diagonal strains in the four atomic layers that constitute the (2/2) SPS in structure 1 for the clamped and unclamped cases are shown in Figs. 4.2 and 4.3, respectively. The lateral alloy modulation considered is described by Eq. 4.1 with $x_m = 0.8$ and $b = 7a_{[110]}$. For best illustration, we show diagonal strains in a rotated frame, in which x' is $[1\bar{1}0]$, y' is $[110]$, and z' is $[001]$. The layer number in the figure labels the atomic layers in Fig. 4.1(a), starting from the bottom layer. There are two main features worth pointing out in Figs. 4.2 and 4.3. First, in the ideal situation (without atomic relaxation),

one would predict $\epsilon_{y'y'}$ to be the same as $\epsilon_{x'x'}$ due to symmetry. However, with atomic relaxation, all Ga(In) atoms tend to shift in a direction so as to reduce the strain in the Ga(In)-rich region. Thus, the magnitude of $\epsilon_{y'y'}$ on Ga(In) sites (dashed lines) is lower (higher) than $\epsilon_{x'x'}$ in Ga(In)-rich region. Second, the z' component strain (dash-dotted lines) tends to compensate the other two components such that the volume of each bulk unit cell is closer to that for the unstrained bulk. Thus, we see that $\epsilon_{z'z'}$ has an opposite sign compared to $\epsilon_{x'x'}$ or $\epsilon_{y'y'}$ at all atomic sites.

Comparing Fig. 4.2 with Fig. 4.3, we see that the main difference between the clamped and unclamped case is that in the atomic layers with lateral composition modulation (layers 2 and 4), the hydrostatic strain (sum of all three diagonal strain components) is much smaller in the unclamped structure than in the clamped structure. This would lead to a major difference in the band-edge profile for the two structures to be discussed below.

The difference in $\epsilon_{x'x'}$ and $\epsilon_{y'y'}$ leads to a nonzero shear strain $e_{xy} = (\epsilon_{y'y'} - \epsilon_{x'x'})/2$ in the original coordinates. For the clamped case, the shear strain is found to be particularly strong near the boundary where the alloy composition

begins to change, and it is sensitive to the degree of lateral alloy mixing. For $x_m = 0.8$ and $b = 7a_{[110]}$, the maximum value of ϵ_{xy} is around 0.4%. For abrupt composition modulation ($x_m = 1$ and $b = 0$) the maximum ϵ_{xy} value increases five-fold to around 2%. The other shear strain components (ϵ_{xz} and ϵ_{yz}) are found to have similar magnitude. For the unclamped case, the shear strain is strong even in regions away from the boundary, and the maximum shear strain is larger than its counterpart in the clamped structure by about 30%.

The diagonal strains of structure 2 for the unclamped case with $x_m = 1$ and $b = 7a_{[110]}$ are shown in Fig. 4.4. The layer number in the figure labels the atomic layers in Fig. 4.1(b), starting from the bottom layer. Only four representative atomic layers (3,4,5, and 7) are shown. We note that the average magnitude of the hydrostatic strain in the In-rich region in model structure 2 is comparable to that for unclamped structure 1.

B. Electronic and optical properties

In order to understand the aspect of lateral quantum confinement due to composition modulation and strain, we examine the band-edge energies of a

strained quantum well structure whose well material is the same as appeared in the self-assembled QWR with a fixed value of y' and the barrier consists of 60 Å thick $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$. For structure 1 depicted in Fig. 4.1(a), the well material consists of 8 pairs of $(\text{GaAs})_2/(\text{InAs})_2$ SPS. The conduction band minimum and valence band maximum of the above quantum well with varying degree of lateral alloy mixing as functions of y' are shown in Fig. 4.5 for both clamped and unclamped cases. The strain Hamiltonian used here is the same as that used in the self-assembled QWR at the corresponding y' . All material parameters are chosen to be the same as in Ref. [9] at 77K, except that the deformation potential c_1 of GaAs is slightly modified from -6.8 eV to -7.1 eV so that $a_1 + a_2 + c_1 = -9.8$ eV is in agreement with the experimental measurements[26] and the valence-band offset between GaAs and InAs used here is 0.26 eV according to the model solid theory[27]. To correct the band gap of SPS and InGaAs alloy due to the bowing effect, we add a correction term $-0.4x(1-x)$ eV to the diagonal element for the s -like bond orbital in the Hamiltonian, where x is the effective alloy composition of the SPS or alloy at a given y' . With the correction of bowing effect, our model gives band gaps

for the $(\text{GaAs})_2(\text{InAs})_2$ SPS, $\text{Ga}_{1-x}\text{In}_x\text{As}$ alloy, and the superlattice made of $(\text{GaAs})_2(\text{InAs})_2$ SPS grown on InP substrate all in very good agreement with available experimental observations. The PL measurements indicate that the $(\text{GaAs})_2(\text{InAs})_2$ SPS grown on InP substrate has a band gap around 0.75 eV.[28] Here we obtain a band gap of 0.74 eV for the $(\text{GaAs})_2(\text{InAs})_2$ SPS with a strain distribution obtained again via the VFF model and 0.79 eV for 8 pairs or 100 Å of $(\text{GaAs})_2(\text{InAs})_2$ SPS sandwiched between $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ confining barriers. This is also consistent with the PL measurements on the $(\text{GaAs})_2(\text{InAs})_2/\text{InP}$ multiple quantum wells.[28]

The band-edge profiles shown in Fig. 4.5 suggest that for the clamped case with alloy mixing, both electrons and holes are confined in the Ga-rich region with an effective barrier height around 0.13 eV for the electrons and 0.1 eV for the holes. Both offsets are large enough to give rise to strong lateral confinement for electrons and holes in the Ga-rich region. Without alloy mixing, the electrons are not well confined, since the average energy between the Ga-rich and In-rich regions are nearly the same. For the unclamped case, both electrons and holes are confined in the In-rich region with an effective

barrier height around $0.2 - 0.3\text{eV}$ for the electrons and $0.1 - 0.2\text{ eV}$ for the holes. We note that the band gap in the In-rich region is rather insensitive to the alloy mixing, while the effective barrier height can change substantially due to different alloy mixing. This is because the band gap changes in In-rich region due to the alloy mixing alone and due to the change in strain distribution happen to nearly cancel each other for the degree of mixing considered here.

Figure 4.6 shows the band-edge profiles for structure 2 [8 pairs of (2/2.25) SPS sandwiched between $60\text{\AA}$ $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ barriers] with and without alloy mixing for both clamped and unclamped cases. For the clamped case, the electrons are confined in the In-rich region, while the holes are confined in the Ga-rich region. Thus, we have a spatially indirect QWR, which will have very weak interband optical transition strength. For the unclamped case, the band-edge profile is similar to the unclamped case of structure 1 with both the electrons and holes confined in the In-rich region. The band gaps for all cases of structure 2 are consistently smaller than their counterparts in structure 1.

Figure 4.7 shows the near zone-center valence subband structures and squared optical matrix elements (P^2) for the QWR model structure 1 with clamped case and without considering alloy mixing. Here P^2 is defined as $\frac{2}{m_0} \sum_{s,s'} | \langle \psi_v | \hat{\epsilon} \cdot \mathbf{p} | \psi_c \rangle |^2$, where ψ_v (ψ_c) denotes a valance (conduction) subband state. The symbol $\sum_{s,s'}$ means a sum over two nearly degenerate pairs of subbands in the initial and final states. $\hat{\epsilon}$ denotes the polarization vector of light. We consider only the x' (along the QWR axis) and y' (perpendicular to the QWR axis) components of the polarization vector. Only the dispersion along the k_1 ($[1\bar{1}0]$) direction is shown in Fig. 4.7, since the dispersion along the k_2 direction for the confined levels is rather small due to strong lateral confinement. All subbands are two-fold degenerate at the zone center due to the Kramer's degeneracy and they split at finite wave vectors as a result of lack of inversion symmetry in the system. The first three pairs of subbands are labeled V1, V2, and V3. They have unusually large energy separations compared with other valence subbands. This is because the first three pairs of subbands represent QWR confined states, whereas the other valence subbands are unconfined in the y' direction.

To examine the effects caused by the shear strain, we have also calculated the band structures with the shear strain set to zero. We found that without the shear strain the first pairs of valence subbands (V1) have much larger dispersion along the k_1 direction with an effective mass along $[1\bar{1}0]$ about a factor five smaller than that with the shear strain. This indicates that the V1 subband states for the case without shear strain are derived mainly from bond orbitals with x' -character, which leads to stronger overlap between two bond orbitals along the x' direction, hence larger dispersion along k_1 . When the shear strain is present, the character of bond orbitals in the V1 subband states change from x' -like to predominantly y' -like; thus, the dispersion along k_1 becomes much weaker. This explains the very flat V1 subbands as shown in Fig. 4.7. The switching of orbital character in the V1 subbands can be understood as follows. When the shear strain is absent, we have $\epsilon_{x'x'} = \epsilon_{y'y'}$, and the confinement effect in the y' direction pushes down the states with y' character (which has smaller effective mass in the y' direction), thus leaving the top valence subband (V1) to have predominantly x' character. On the other hand, with the presence of shear strain as shown in structure

1, we have $\epsilon_{y'y'} < \epsilon_{x'x'}$ in Ga-rich region, and the bi-axial term of the strain potential forces the y' -like states to move above the x' -like states, overcoming the confinement effect. As a result, the V1 subbands become y' -like. The conduction subbands are approximately parabolic as usual with a zone-center subband minimum equal to 688 meV. This gives an energy gap of 763 meV for QWR model structure 1. As seen in Fig. 4.7, the C1-V1 transition strength for y' -polarization (dashed line) is more than twice that for the x' -polarization (solid line) [$P_{[\bar{1}\bar{1}0]}^2/P_{[110]}^2 \approx 0.36$]. This is consistent with the fact that the bond orbitals involved in the V1 subbands are predominantly y' -like.

We have also studied the case with alloy mixing for clamped structure 1 in which a gradual lateral modulation in In composition substantially reduces the shear strain. Using a lateral alloy mixing described in Eq. 4.1 with $x_m = 0.8$ and $b = 7a_{[110]}$, we find significant change in band structures and optical properties compared to the case without alloy mixing. With alloy mixing we found that the first pairs of valence subbands (V1) have much larger dispersion than their counterparts in Fig. 4.7, and the atomic character in the V1 states changes from predominantly y' -like to x' -like. The change of

atomic character in the V1 states is a consequence of the competition between the QWR confinement which suppresses the y' character and the e_{xy} shear strain which suppresses the x' character. As a result, the ratio $P_{[\bar{1}\bar{1}0]}^2/P_{[110]}^2$ changes from 0.36 to 3.5, indicating a reversal of optical anisotropy.

Next, we study the properties of unclamped self-assembled QWRs. We find that for this case, the electrons and holes are always confined in the In-rich region, regardless of the degree of alloy mixing and whether the QWR structure consists of (2/2) SPS or (2/2.25) SPS. Furthermore, since the strain in the In-rich region has opposite sign compared to that in the Ga-rich region, the shear strain has an opposite effect on the VB states confined in the In-rich region versus the Ga-rich region. Namely, it pushes the energy of the y' -like VB states down relative to the x' -like VB states. Thus, both the QWR confinement and the shear strain effects are in favor of giving a predominantly x' character in the V1 subband. Therefore, the interband optical transition always has a ratio $P_{[\bar{1}\bar{1}0]}^2/P_{[110]}^2$ larger than 1.

To illustrate this, we show in Fig. 4.8 the near zone-center valence subband structures and squared optical matrix elements (P^2) for the QWR model

structure 1 as depicted in Fig. 4.1(a) with thin capping layer and with alloy mixing described by $x_m = 0.8$ and $b = 7a_{[110]}$. Comparing the band structure in Fig. 4.8 with that in Fig. 4.7, we see that the V1 subband has much larger dispersion (i.e. much smaller effective mass) than its counterpart in Fig. 4.7. There are two reasons for this. First, the holes in the unclamped case are now confined in the In-rich region rather than in the Ga-rich region as in the clamped case, thus having much smaller effective mass. Second, both the QWR confinement and the shear strain effects lead to a predominantly x' character in the V1 states, which tend to yield a smaller effective mass in the k_1 direction. The optical properties shown in Fig. 4.8 are also distinctly different from that shown in Fig. 4.7. The interband optical transition (C1-V1) now shows a much stronger polarization along $[1\bar{1}0]$ than $[110]$. The quick drop of the y' polarization in C1-V1 transition at $k_1 \approx 0.035\frac{2\pi}{a}$ is caused by the band mixing of V1 and V2 states as can be seen in the VB band structures in this figure.

We have also calculated the near zone-center valence subband structures and squared optical matrix elements (P^2) for the QWR model structure 2

with thin capping layer (not shown), and we find that the band structures and optical matrix elements are similar to Fig. 4.8, except that the energy separation between V1 and V2 subbands is smaller (by ~ 5 meV) and the polarization ratio ($P_{[1\bar{1}0]}^2/P_{[110]}^2$) is larger.

Finally, we list in Table 4.1 the band gaps and the polarization ratio ($P_{[1\bar{1}0]}^2/P_{[110]}^2$) for various QWR structures with varying degrees of lateral alloy mixing (as indicated by the parameters x_m and b) with the last line as the experimental results. To calculate the polarization ratio in the PL spectra, we integrate the squared optical matrix element over the range of k_1 corresponding to the spread of exciton envelope function in the k space. The exciton envelope function is obtained by solving the 1D Schrödinger equation for the exciton in the effective-mass approximation similar to what we did in Ref. 9. This table allows one to see the trend of optical properties as the degree of lateral alloy mixing varies and as the structure changes from (2/2) SPS to (2/2.25) SPS. For clamped (2/2) SPS structure, the band gap is insensitive to alloy mixing, but the polarization ratio changes drastically due to the shear strain effect. The clamped (2/2.25) SPS structure is spatially indirect, hence

is not listed here. For unclamped (2/2) SPS structure, the band gap varies between 0.77 and 0.8 eV and the polarization ratio changes from 3.1 to 1.5 as the degree of alloy mixing is increased. For unclamped (2/2.25) SPS structure, both the band gap (around 0.74 eV) and the polarization ratio (around 2) are insensitive to the change in degree of alloy mixing.

Experimentally, the PL peak for self-assembled InGaAs QWRs with similar dimensions as considered in our model structures is around 735 meV and the polarization ratio for different samples is found to be between 2 and 4.[4-6] Taking into account an exciton binding energy between 10 and 20 meV, we find that our theoretical predictions for both unclamped and clamped structures with lateral alloy mixing (after we included the bowing correction for InGaAs alloy and SPS) are consistent with the experimental findings. Since different samples can have different structures, it requires more detailed information about the electronic states (such as the energy levels of various electron and hole subbands and the associated interband transition strengths) in order to determine the actual geometry. Such information may be obtained via comparison between the theory and experiment for the in-

terband or inter-subband absorption spectra.

V. CONCLUSION

We have calculated the band structures and optical matrix elements for the self-assembled GaInAs QWR grown by the SILO method. The actual SPS structure and the microscopic strain distribution have been taken into account. The effects of microscopic strain distribution on the valence subband structures and optical matrix elements are studied for two types of self-assembled QWR structures, one with (2/2) SPS structure and the other with (2/2.25) SPS structure, with varying degrees of lateral alloy mixing. The clamping effect due to thick capping layer is also examined. The VFF model is used to calculate the equilibrium atomic positions in the QWR model structures. This allows the calculation of the strain distribution at the atomistic level.

We find that in model structures with thick capping layer (clamped case), the magnitude of shear strain is quite large, around 2%, when the lateral alloy mixing is absent, and it reduces substantially when the lateral alloy mixing

is introduced. We found that the shear strain effect can alter the valence subband structures substantially when the holes are confined in the Ga-rich region, and it gives rise to a reversed optical anisotropy (i.e. $P_{[1\bar{1}0]}^2 < P_{[110]}^2$) compared with QWR structures with negligible shear strain. This points to a possibility of "shear strain-engineering" to obtain QWR laser structures of desired optical anisotropy. For model structures with thin capping layer (unclamped case), the effect of shear strain is less dramatic, since the holes are confined in the In-rich region, where both the QWR confinement and the shear strain have similar effect. We found that polarization ratio ($P_{[1\bar{1}0]}^2/P_{[110]}^2$) for the unclamped case is always larger than 1 for both (2/2) and (2/2.25) SPS structures, regardless of the degree of lateral alloy mixing.

The band gap and polarization ratio obtained for both clamped and unclamped (2/2) SPS structures with lateral alloy mixing ($x_m \approx 0.8$) and for unclamped (2/2.25) SPS structures are consistent with experimental observations on most self-assembled InGaAs QWRs with similar specifications. For clamped (2/2) SPS structure without alloy mixing, we predicted a reversed optical anisotropy compared with the PL measurements for most InAs/GaAs

self-assembled QWRs. However, there exist a few InAs/GaAs self-assembled QWR samples which display the reversed optical anisotropy at 77 K[7], and recent experimental studies also indicated a reversed optical anisotropy in many samples at 300 K.[6] Our studies demonstrated a possibility for the reversed optical anisotropy that is due to the shear strain effect. There may be other possibilities for the reversed optical anisotropy at 300K. For example, the thermal population of the excited hole states, which have different atomic characters from the lowest-lying hole states as may also lead to a change in the polarization ratio. The temperature dependence of the PL peak position and polarization in self-assembled InGaAs QWRs[6] remains an intriguing question to be addressed in the future.

TABLES

TABLE I. List of band gaps and polarization ratios for all structures studied

x_m	b/a_{110}	alloy mixing	clamped/unclamped	SPS structure	gap(eV)	$P_{\parallel}^2/P_{\perp}^2$
1.0	0	no	clamped	(2/2)	0.765	0.36
0.8	7	yes	clamped	(2/2)	0.763	3.5
1.0	0	no	unclamped	(2/2)	0.791	3.1
0.7	7	yes	unclamped	(2/2)	0.766	1.8
0.6	7	yes	unclamped	(2/2)	0.80	1.82
0.6	15	yes	unclamped	(2/2)	0.798	1.5
1.0	0	no	unclamped	(2/2.25)	0.731	2.2
1.0	7	yes	unclamped	(2/2.25)	0.74	2.1
Expts[4]					0.735	2-4

REFERENCES

- ¹ A. R. Adams, Electron. Lett. **22**, 249 (1986).
- ² E. Yablonovitch and E. O. Kane. IEEE J. Lightwave Technol. LT-4, 504 (1986).
- ³ G. P. Agrawa and N. K. Dutta, Long Wavelength Semiconductor Lasers, 2nd ed. (Van. Nostrand Reinhold, New York, 1993) Chap.7.
- ⁴ S.T. Chou, K. Y. Cheng, L. J. Chou, and K. C. Hsieh, Appl. Phys. Lett. **17**, 2220 (1995); J. Appl. Phys. **78** 6270, (1995); J. Vac. Sci. Tech. B **13**, 650 (1995); K. Y. Cheng, K. C. Hsien, and J. N. Baillargeon, Appl. Phys. Lett. **60**, 2892 (1992).
- ⁵ D. E. Wohlert, S. T. Chou, A. C Chen, K. Y. Cheng, and K. C. Hsieh, Appl. Phys. Lett. **17**, 2386 (1996).
- ⁶ D.E. Wohlert, and K. Y. Cheng, Appl. Phys. Lett. **76**, 2249 (2000).
- ⁷ D.E. Wohlert, and K. Y. Cheng, private communications.
- ⁸ Y. Tang, H. T. Lin, D. H. Rich, P. Colter, and S. M. Vernon, Phys. Rev. B **53**, R10501 (1996).

- ⁹ Y. Zhang and A. Mascarenhas, Phys. Rev. B **57**, 12245 (1998).
- ¹⁰ L. X. Li and Y. C. Chang, J. Appl. Phys. **84** 6162, 1998.
- ¹¹ T. Mattila, L. Bellaiche, L. W. Wang, and A. Zunger, Appl. Phys. Lett., **72**, 2144 (1998).
- ¹² L. W. Wang, J. Kim, and A. Zunger, Phys. Rev. B **59**, 5678 (1999).
- ¹³ H. Jiang and J. Singh, Phys. Rev. B **56**, 4696(1997).
- ¹⁴ P. N. Keating, Phys. Rev. **145**, 637(1966).
- ¹⁵ R. M. Martin, Phys. Rev. B **1**, 4005(1969).
- ¹⁶ Y. C. Chang, Phys. Rev. B **37**, 8215 (1988).
- ¹⁷ Mau-Phon Houng and Y.C Chang, J. Appl. Phys. **65**, 3096 (1989).
- ¹⁸ M. Grundmann, O.Stier, and D. Bimberg, Phys. Rev. B **52**,11969 (1995).
- ¹⁹ O.Stier, M.Grundmann, and D.Bimberg, Phys. Rev. B **59**, 5688,(1999).
- ²⁰ G. L. Bir and G. E. Pikus, Symmetry and Strain Induced Effects in Semiconductors (Halsted, United Kingdom, 1974); L.D. Landau and E. L. Lifshitz, Theory of Elasticity (Addison-Wesley Publishing Company Inc, Read-

ing, Massachusetts, USA, 1970).

²¹ C. Pryor, J. Kim, L.W. Wang, A.J. Williamson and A. Zunger, Phys. Rev. **B183**, 2548(1998).

²² S. Adachi, J. Appl. Phys. **53**, 8775 (1982).

²³ H. Mathieu, P. Meroe, E. L. Amerziane, B. Archilla, J. Camassel, and G. Poiblaud, Phys. Rev. B**19**, 2209 (1979); S. Adachi and C. Hamaguchi, Phys. Rev. B**19**, 938 (1979).

²⁴ J. M. Hinckley and J. Singh, Phys. Rev. B**42**, 3546 (1990).

²⁵ O. Madelung and M. Schulz, Landolt-Börstein, New Series III/22a, p. 87 (1982).

²⁶ A. Blacha, H. Presting, M Cardona, Phys. Stat. Sol. (b) **126**, 11 (1984).

²⁷ C. G. Van de Walle, Phys. Rev. B **39**, 1871 (1989).

²⁸ M. Razeghi, Ph. Maurel, F. Omnes, and J. Nagle, Appl. Phys. Lett. **51**, 2216 (1987).

FIGURES

FIG. 1. Schematic sketch of the unit cell of the self-assembled quantum wire for two model structures considered. Each unit cell consists of 8 pairs of (2/2) or (2/2.25) GaAs/InAs short-period superlattices (SPS). In structure 1, the (2/2) SPS contains four diatomic layers (only the cation planes are illustrated) and the SPS is repeated eight times. In structure 2, four pairs of (2/2.25) SPS (or 17 diatomic layers) form a period, and the period is repeated twice in the unit cell. Filled and open circles indicate Ga and In rows (each row extends infinitely along the $[1\bar{1}0]$ direction).

FIG. 2. Diagonal strain distribution of model structure 1 [corresponding to Fig. 4.1(a)] with thick capping layer (clamped case). Solid: $\epsilon_{x'x'}$. Dashed: $\epsilon_{y'y'}$. Dash-dotted: $\epsilon_{z'z'}$. Parameters for alloy mixing: $x_m = 0.8$ and $b = 7a_{[110]}$.

FIG. 3. Diagonal strain distribution of model structure 1 with thin capping layer (unclamped case). Solid: $\epsilon_{x'x'}$. Dashed: $\epsilon_{y'y'}$. Dash-dotted: $\epsilon_{z'z'}$. Parameters for alloy mixing: $x_m = 0.8$ and $b = 7a_{[110]}$.

FIG. 4. Diagonal strain distribution of model structure 2 [corresponding to Fig. 4.1(b)] with thin capping layer (unclamped case). Solid: $\epsilon_{x'x'}$. Dashed: $\epsilon_{y'y'}$. Dash-dotted: $\epsilon_{z'z'}$. Parameters for alloy mixing: $x_m = 0.8$ and $b = 7a_{[110]}$.

FIG. 5. Conduction and valence band edges for 8 pairs of (2/2) SPS structures sandwiched between $60\text{\AA}\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ barriers with different degrees of lateral alloy mixing as functions of the $[110]$ coordinate y' for both clamped (thick capping layer) and unclamped (thin capping layer) case. In upper panel, the dashed line is for abrupt modulation (without alloy mixing) and the solid line is for lateral alloy mixing with $x_m = 0.8$ and $b = 7a_{[110]}$. In lower panel, dash-dotted: without alloy mixing; solid: $x_m = 0.7$ and $b = 7a_{[110]}$; dotted: $x_m = 0.6$ and $b = 7a_{[110]}$; dashed: $x_m = 0.6$ and $b = 15a_{[110]}$.

FIG. 6. Conduction and valence band edges for 8 pairs of (2/2.25) SPS structures sandwiched between $60\text{\AA}\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ barriers with different degrees of lateral alloy mixing as functions of the $[110]$ coordinate y' for both clamped (thick capping layer) and unclamped (thin capping layer) case. Dashed: without alloy mixing. Solid: with alloy mixing described by $x_m = 1.0$ and $b = 7a_{[110]}$.

FIG. 7. Valance subband structures and squared optical matrix elements for self-assembled QWR made of (2/2) SPS structure with thick capping layer (clamped case) and without alloy mixing.

FIG. 8. Valance subband structures and squared optical matrix elements for self-assembled QWR made of (2/2) SPS structure with thin capping layer (unclamped case) and with alloy mixing described by $x_m = 0.8$ and $b = 7a_{[110]}$.

I. INTRODUCTION

Quantum-well infra-red photodetectors (QWIP's) have been extensively studied in recent years.¹⁻⁵ The main mechanism used in QWIPs is the inter-subband optical transition, because the wavelengths for these transitions in typical III-V quantum wells can be tailored to match the desired operating wavelength for infra-red (IR) detection. Due to its narrow band absorption, QWIP's are complementary to the traditional HgCdTe detectors, which utilize the inter-band absorption, and therefore are applicable only for broad-band absorption. QWIP's based on III-V semiconductor quantum wells have been shown to be promising candidate for making flat-panel high-density IR imaging arrays used in IR detectors.² The main drawback of QWIP's is the lack of normal-incidence capability, unless some processing is made to create diffraction gratings on the surface, which tends to reduce the responsivity of the material to the incident radiation.² Because electrons in quantum wells have translational invariance (within the effective-mass model) in the plane normal to the growth axis, the electron inter-subband transitions for normal-incident radiation is zero (or very small even if the coupling with other bands is considered). One way to break the translational invariance is to introduce the surface diffraction grating as commonly adopted in many QWIP's fabricated today. A better (and less expensive) way to break the in-plane translational invariance is to utilize the strain-induced lateral modulation provided in self-assembled nano-structure ma-

terials. These nano-structures include quantum wires^{6–18} and quantum dots.^{19–23} Because the lateral modulation is formed via self-assembly, the fabrication of this type of materials will be much more efficient once the optimized growth parameters are known. Hence, it will be cost effective to use them for device fabrications.

Self-assembled III-V QWR's grown via the strain-induced lateral-layer ordering (SILO) process have attracted a great deal of attention recently.^{12–18} The self-assembly process occurs during the growth of short-period superlattices (SPS) [e.g. (GaAs)₂/(InAs)_{2.25}] along the [001] direction on an InP substrate. The excess fractional InAs layer leads to stripe-like islands during the initial MBE growth.¹² The presence of stripes combined with strain leads to natural phase separation as additional layers of GaAs or InAs are deposited and the structure becomes laterally modulated in terms of In/Ga composition. A self-assembled QWR heterostructure can then be created by sandwiching the laterally modulated layer between barrier materials such as Al_{0.24}Ga_{0.24}In_{0.52}As (quaternary), Al_{0.48}In_{0.52}As (ternary), or InP (binary).^{12–18}

It was found that different barrier materials can lead to different degree of lateral composition modulation, and the period of lateral modulation ranges from 100 Å to 300 Å depending on the growth time and temperature.²⁴

In this chapter, we explore the usefulness of InGaAs quantum wires (QWR's) grown by the strain-induced lateral ordering (SILO) process for IR detection. Our theoretical modeling includes the effects of realistic band structures and microscopic strain distributions by combining the effective bond-orbital model (EBOM)²⁵ with the valence-force-field (VFF)

model.^{26–28} One of the major parameters for the IR detectors is the absorption quantum efficiency which is directly related to the absorption coefficient by $\eta = 1 - e^{-\alpha l}$ where α is the absorption coefficient and l is the sample length.²⁹ Thus, to have a realistic assessment of the material for device application, we need to perform detailed calculations of the absorption coefficient, taking into account the excitonic and band structure effects. Both inter-subband and inter-band transitions are examined systematically for a number of structure parameters (within the experimentally feasible range) chosen to give the desired effect for IR detection.

It is found that the wavelengths for the inter-subband transitions of InGaAs self-assembled QWR's range from 10 to 20 μm , while the inter-band transitions are less than 1.5 μm . Thus, the material provides simultaneous IR detection at two contrasting wavelengths, something desirable for application in multi-colored IR video camera.

Several structure models with varying degrees of alloy mixing for lateral modulation are considered. For the inter-band absorption, the excitonic effect is important, since it gives rise to a large shift in transition energy and substantial enhancement of the absorption spectrum. To study the excitonic effect on the absorption spectrum for both discrete and continuum states, we use a large set of basis functions with a finite-mesh sampling in the k-space and diagonalize the exciton Hamiltonian directly. Emphasis is put on the analysis of line shapes of various peak structures arising from discrete excitonic states of one pair of subbands coupled with the excitonic (discrete and continuum) states associated with other pairs of subbands. We find that the excitonic effect enhances the first absorption peak around 1.2-1.5 times and shifts the peak position by 20-50meV.

II. THEORETICAL MODEL

The QWR structures considered here consist of 8 pairs of $(\text{GaAs})_2(\text{InAs})_{2.25}$ short-period superlattices (SPS) sandwiched between $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}\text{As}$ barriers. The SPS structure prior to strain induced lateral ordering (SILO) is depicted in Fig. 4.1(b). With lateral ordering, the structure is modeled by a periodic modulation of alloy composition in layers with fractional monolayer of (In or Ga) in the SPS structure. In layers 7 and 9 (starting from the bottom as layer 1), we have

$$x_{\text{In}} = \begin{cases} x_m[1 - \sin(\pi y'/2b)]/2 & \text{for } y' < b \\ 0 & \text{for } b < y' < L/2 - b \\ x_m\{1 + \sin[\pi(y' - L/2)/2b]\}/2 & \text{for } L/2 - b < y' < L/2 + b \\ x_m & \text{for } L/2 + b < y' < L - b \\ x_m\{1 - \sin[\pi(y' - L)/2b]\}/2 & \text{for } y' > L - b, \end{cases} \quad (1)$$

where x_m is the maximum In composition in the layer, $2b$ denotes the width of lateral composition grading, and L is the period of the lateral modulation in the $[110]$ direction. The experimental feasible range of L is between 100 Å and 300 Å. The length of L is controlled by the growth time and temperature.

In layers 3 and 13, we have

$$x_{\text{In}} = \begin{cases} 0 & \text{for } 0 < y' < 5L/8 - b \\ x_m \{1 + \sin[\pi(y' - 5L/8)/2b]\}/2 & \text{for } 5L/8 - b < y' < 5L/8 + b, \\ x_m & \text{for } 5L/8 + b < y' < 7L/8 - b \\ x_m \{1 - \sin[\pi(y' - 7L/8)/2b]\}/2 & \text{for } 7L/8 - b < y' < 7L/8 + b \\ 0 & \text{for } 7L/8 + b < y' < L. \end{cases} \quad (2)$$

Similar equation for x_{Ga} in layers 5 and 11 can be deduced from the above. By varying the parameters x_m and b , we can get different degrees of lateral alloy mixing. Typically x_m is between 0.6 and 1, and b is between zero and $15a_{[110]} \approx 62 \text{ \AA}$.

A VFF model^{26–28} is used to find the equilibrium atomic positions in the self-assembled QWR structure by minimizing the lattice energy. The strain tensor at each atomic (In or Ga) site is then obtained by calculating the local distortion of chemical bonds. Once the microscopic strain distribution in the model structure is determined, the energy levels and wave-functions of self-assembled quantum wires are then calculated within the effective bond-orbital model (EBOM). Detailed description of this method can be found in Refs.^{25,30–32}. EBOM used here is a tight-binding-like model in which two s-like conduction bands (including spin) and four valence bands with total angular momentum $J = 3/2$ (due to spin-orbit coupling of p-like orbitals with the spinor). Thus, the present model is comparable to the six-band $\mathbf{k} \cdot \mathbf{p}$ model.

To minimize the computing effort, we express the electron and hole states for the quantum wire structures in terms of eigen-states of a quantum well structure with different in-plane wave vectors. The quantum well consists of 8 pairs of $(\text{GaAs})_2(\text{InAs})_2$ short-period super-

lattice (SPS) plus two InAs monolayers (one inserted after the second pair of SPS and the other after the sixth pair of SPS), so the the total In/Ga composition ratio is consistent with the $(\text{GaAs})_2(\text{InAs})_{2.25}$ SPS. The whole stack of SPS's is then sandwiched between two slabs of $\text{Al}_{0.24}\text{Ga}_{0.24}\text{In}_{0.52}$ barriers. Let us denote the quantum well eigen-states as $|n, k_1, k_2\rangle_{QW}$ where n labels the subbands, k_1 denotes the wave vector along the wire ($[1\bar{1}0]$) direction and k_2 labels the wave vector in the $[110]$ direction, which is perpendicular to the wire and the growth axis. Expanding the quantum well states in terms of bond-orbitals, we have

$$|n, k_1, k_2\rangle_{QW} = \frac{1}{\sqrt{L_s}} \sum_{\alpha, \mathbf{R}} f_{n, k_1, k_2}(\alpha, R_z) \exp(ik_2 R_2) \exp(ik_1 R_1) |u_\alpha(\mathbf{R})\rangle,$$

where L_s is the sample length along the wire axis, $f_{n, k_1, k_2}(\alpha, R_z)$ is the eigen-vector for the quantum well Hamiltonian, and $u_\alpha(\mathbf{R})$ denotes an α -like bond orbital state at site $\mathbf{R}$ ($\alpha = 1, \dots, 6$ for two s-like conduction-band and four $J = 3/2$ valence-band orbitals). Here $\mathbf{R}$ runs over all lattice sites within the SPS layer (well region) and AlGaInAs layer (barrier region).

We then diagonalize the hamiltonian for the quantum wire (QWR) within a basis which consists of the quantum well states with k_2 's separated by reciprocal lattice vectors $g_m = m(2\pi/a_{[110]})$; $m = \text{integers}$. Thus, the QWR states are written as

$$|i, k_1, k_2\rangle = \sum_{n, m} C_{i, k_1}(n, k_2 + g_m) |n, k_1, k_2 + g_m\rangle_{QW}$$

where $C_{i, k_1}(n, k_2 + g_m)$ is the eigen-vector for the quantum-wire hamiltonian matrix for the i -th QWR subband at wave vector (k_1, k_2) .

In terms of the bond orbitals, we can rewrite the QWR states as

$$|i, k_1, k_2\rangle = \sum_{\alpha, \mathbf{R}} F_{i,k_1,k_2}(\alpha, \mathbf{R}) |u_\alpha(\mathbf{R})\rangle$$

where

$$F_{i,k_1,k_2}(\alpha, \mathbf{R}) = \frac{1}{\sqrt{L}} \sum_{n,m} C_{i,k_1}(n, k_2 + g_m) f_{n,k_1,k_2+g_m}(\alpha, R_z) \exp[i(k_2 + g_m)R_2] \exp(ik_1 R_1)$$

is the QWR envelope function. For the laterally confined states, the dispersion of bands versus k_2 is negligible; thus, the k_2 dependence can be ignored.

The absorption coefficient for inter-subband transitions between subbands i and j is given by

$$\alpha_{ij}(\hbar\omega) = \frac{4\pi^2 e^2 \hbar}{n_r m_e^2 c L_z \hbar\omega} \sum_{k_1, k_2} |\langle i, k_1, k_2 | \hat{\epsilon} \cdot \mathbf{p} | j, k_1, k_2 \rangle|^2 [f_i(k_1, k_2) - f_j(k_1, k_2)] \delta(E_j(k_1, k_2) - E_i(k_1, k_2) - \hbar\omega) \quad (3)$$

where n_r is the refractive index of the QWR, L_z is the width of the SPS region (or QW confined in the z direction), $f_i(f_j)$ is the Fermi-Dirac distribution function for subband i (j). The optical matrix elements between QWR subband states are related to those between bond orbitals by

$$\langle i, k_1, k_2 | \hat{\epsilon} \cdot \mathbf{p} | j, k_1, k_2 \rangle = \sum_{\alpha, \alpha', \tau} F_{i,k_1,k_2}^*(\alpha, \mathbf{R}) F_{j,k_1,k_2}(\alpha', \mathbf{R}) \langle u_\alpha(\mathbf{R}) | \hat{\epsilon} \cdot \mathbf{p} | u_{\alpha'}(\mathbf{R} + \vec{\tau}) \rangle,$$

where $\vec{\tau}$ runs over on-site or the 12 nearest-neighbor sites in the fcc lattice. The optical matrix elements between bond orbitals are related to the band parameters by requiring the optical matrix elements between bulk states near the zone center to be identical to those obtained in the $\mathbf{k} \cdot \mathbf{p}$ theory³⁵. We obtain³¹

$$\langle u_s(\mathbf{R}) | p_\alpha u_{\alpha'}(\mathbf{R}) \rangle = \sqrt{m_0 E_p / 2} \delta_{\alpha, \alpha'}; \alpha = x, y, z,$$

$$\langle u_s(\mathbf{R}) | p_\alpha u_s(\mathbf{R} + \vec{\tau}) \rangle = (\hbar/2\sqrt{2}a)(E_p/Eg - m_0/m_e^*)\tau_\alpha; \alpha = x, y, z,$$

where τ_α is the α -th of the lattice vector τ in units of $a/2$, E_p is the inter-band optical matrix element as defined in Ref. 35, and m_e^* is the electron effective mass.

Next, we study the inter-band transitions. For this case, the excitonic effect is important for undoped samples. For heavily doped samples, the excitonic effect can be ignored due to the phase-spacing filling and carrier screening effects. We shall consider both situations. Here we are only interested in the absorption spectrum near the band edge due to laterally confined states. Thus, the dispersion in the k_2 direction can be ignored. Without the excitonic effects, the absorption coefficient is given by Eq. (5.3) with i (j) indicating the valence (conduction) subband states. At low temperatures, the valence subbands are completely filled, so the Fermi-Dirac distribution (f_i) in Eq. (5.3) can be replaced by 1. For undoped samples, the exciton states with zero center-of-mass momentum is written as linear combinations of products of electron and holes states associated with the same k_1 (wave vector along the wire direction). We write the QWR electron-hole product state for the i -th conduction subband and j -th valence subband as

$$|i, j; k_1\rangle = |i, k_1\rangle |j, k_1\rangle$$

$$\equiv \sum_{\alpha, \beta, \mathbf{R}_e, \mathbf{R}_h} F_{i, k_1}(\alpha, \mathbf{R}_e) G_{j, k_1}(\beta, \mathbf{R}_h) |u(\alpha, \mathbf{R}_e) \rangle |u(\beta, \mathbf{R}_h) \rangle.$$

The matrix elements of the exciton Hamiltonian within this basis is given by

$$\langle i, j; k_1 | H_{ex} | i', j'; k'_1 \rangle = [E_i(k_1) - E_j(k_1)] \delta_{i, i'} \delta_{j, j'} \delta_{k_1, k'_1} - \sum_{\mathbf{R}_e, \mathbf{R}_h} \mathcal{F}_{ii'}^*(k_1, k'_1; \mathbf{R}_e) v(\mathbf{R}_e - \mathbf{R}_h) \mathcal{G}_{jj'}(k_1, k'_1; \mathbf{R}_h), \quad (4)$$

where $v(\mathbf{R}_e, \mathbf{R}_h) = \frac{4\pi e^2}{\epsilon(0) |\mathbf{R}_e - \mathbf{R}_h|}$ is the coulomb interaction between the electron and hole screened by the static dielectric constant $\epsilon(0)$, and

$$\mathcal{F}_{ii'}(k_1, k'_1; \mathbf{R}_e) = \sum_{\alpha} F_{i,k_1}^*(\alpha, \mathbf{R}_e) F_{i',k'_1}(\alpha, \mathbf{R}_e)$$

describes the charge density matrix for the electrons. Similarly,

$$\mathcal{G}_{jj'}(k_1, k'_1; \mathbf{R}_h) = \sum_{\beta} G_{j,k_1}^*(\beta, \mathbf{R}_h) G_{j',k'_1}(\beta, \mathbf{R}_h)$$

describes the charge density matrix for the holes. In Eq. (5.4), we have adopted the approximation

$$\langle u(\alpha, \mathbf{R}_e), u(\beta, \mathbf{R}_h) | v | u(\alpha', \mathbf{R}'_e), u(\beta', \mathbf{R}'_h) \rangle \approx v(\mathbf{R}_e - \mathbf{R}_h) \delta_{\alpha, \alpha'} \delta_{\beta, \beta'} \delta_{\mathbf{R}_e, \mathbf{R}'_e} \delta_{\mathbf{R}_h, \mathbf{R}'_h},$$

since the Coulomb potential is a smooth function over the distance of a lattice constant, except at the origin, and the bond orbitals are orthonormal to each other. At the origin ($\mathbf{R}_e = \mathbf{R}_h$), the potential is singular, and we replace it by an empirical constant which is adjusted so as to give the same exciton binding energy as obtained in the effective-mass theory for a bulk system. The results are actually insensitive to the on-site Coulomb potential parameter, since the Bohr radius of the exciton is much larger than the lattice constant.

After the diagonalization, we obtain the excitonic states as linear combinations of the electron-hole product states, and the inter-band absorption coefficient is computed according to

$$\alpha^{ex}(\hbar\omega) = \frac{4\pi^2 e^2 \hbar}{n_r m_e^2 c A \hbar\omega} \sum_n \left| \sum_{k_1, i, j} C_{ij}^n(k_1) \hat{\epsilon} \cdot \mathbf{p}_{ij}(k_1) \right|^2 \delta(\hbar\omega - E_n^{ex}), \quad (5)$$

where A is the cross-sectional area of the SPS region within the QWR unit cell (as depicted in Fig. 5.1). $C_{ij}^m(k_1)$ is the n -th eigen-vector obtained by diagonalizing the exciton Hamiltonian of Eq. (5.4). The momentum matrix elements $\mathbf{p}_{ij}(k_1)$ are given by

$$\mathbf{p}_{ij}(k_1) = \sum_{\alpha, \beta, \vec{\tau}} F_{i, k_1}^*(\alpha, \mathbf{R}_e) G_{j, k_1}(\beta, \mathbf{R}_h + \vec{\tau}) \langle u_\alpha(\mathbf{R}_e) | \hat{\epsilon} \cdot \mathbf{p} | u_\beta(\mathbf{R}_h + \vec{\tau}) \rangle. \quad (6)$$

In the absence of band mixing, the conduction subband state reduces to a pure s -like state and the valence subband state reduces to a pure p -like state. In that case, only the element $\langle u_s(\mathbf{R}_e) | p_\alpha | u_{p_\alpha}(\mathbf{R}_e) \rangle = \sqrt{m_0 E_p / 2}$ is needed, and the results become similar to that obtained by the effective mass method.

In order to obtain a smooth absorption spectrum, we replace the δ function in Eq. (5.1) by a Lorentzian function with a half-width Γ ,

$$\delta(E_i - E) \approx \Gamma / \{\pi[(E_i - E)^2 + \Gamma^2]\}, \quad (7)$$

where Γ is energy width due to inhomogeneous broadening, which is taken to be 0.02 eV.

III. RESULTS AND DISCUSSIONS

We have performed calculations of inter-subband and inter-band absorption spectra[36] for the QWR structure depicted in Fig. 4.1(b) with varying degree of alloy mixing and different lengths of period (L) in the lateral modulation. We find that the inter-subband absorption spectra are sensitive to the length of period (L), but rather insensitive to the degree of alloy mixing. Thus, we only present results for the case with moderate alloy

mixing, which are characterized by parameters $b = 33\text{\AA}$ and $x_m = 1.0$. In the calculations of strain distribution via the VFF model, the bottom layer atoms of QWR's are bounded by the InP substrate, while the upper layer atoms and GaAs capping layer atoms are allowed to move freely. This structure corresponds to the unclamped structure as indicated in Ref. 34.

For different period length (L) of QWR's, the strain distribution profiles are qualitatively similar as shown in Ref. 34. As L decreases, the hydrostatic strain in In-rich region (the right half of QWR unit cell shown in Fig. 4.1(b)) increases, while it decreases in the Ga-rich region (the left half of QWR unit cell). The bi-axial strain components vary with L in the opposite way in comparison to the hydrostatic component.

Figure 5.1 depicts the potential profiles due to strain-induced lateral ordering seen by an electron in two QWR structures considered here ($L = 50a_{[110]}$ and $L = 40a_{[110]}$). Solid(Dashed) lines are for model structures with (without) alloy mixing. From the potential profile, we see that both the electron and hole in the ground state are laterally confined in the In-rich region (the right half of the QWR unit cell).

The conduction subband structures for the self-assembled QWRs with alloy mixing ($x_m = 1.0$ and $b = 8a_{[110]}$) for ($L = 50a_{[110]}$ and $L = 40a_{[110]}$) are shown in Fig. 5.2. All subband are grouped in pairs with a weak spin splitting (not resolved on the scale shown). The first (C1) and third (C3) pairs of subbands are nearly dispersionless along the k_2 direction, while the second (C2) and fourth (C4) pairs of subbands have appreciable dispersion. Comparing the envelope functions for the first four pairs of conduction subband states (C1-C4)

with the solutions to rectangular quantum box solutions labeled by principal quantum numbers (n_y, n_z) , we can identify them as the (1,1), (2,1), (1,2), and (3,1) states, respectively. Thus, the C1 and C3 states are well confined in the lateral direction, and the corresponding subbands are nearly dispersionless in k_2 . On the other hand, the C2 and C4 states are less confined in the y' direction due to the larger spread of their y' component wave function (with higher principal quantum numbers) and the corresponding subbands have appreciable dispersion along k_2 . The inter-subband transition between the first two pairs (C1-C2) gives rise to the dominant IR response. For $L = 40a_{[110]}$, the C2 and C3 subbands are nearly degenerate for $k_2 = 0$ (due to accidental degeneracy), and the (2,1) and (1,2) characters are strongly mixed. However, for finite k_2 , the degeneracy is removed [due to the large dispersion of the (2,1) state] and they are no longer mixed.

The valence subband structures for the self-assembled QWRs with alloy mixing ($x_m = 1.0$ and $b = 33\text{\AA}$) for ($L = 50a_{[110]}$ and $L = 40a_{[110]}$) are shown in Fig. 5.3. All valence subbands display substantial spin splitting along k_1 and the first four pairs (V1 – V4) of subbands are nearly dispersionless along k_2 , indicating strong lateral confinement effect. The valence subbands with energies below -130meV correspond to unconfined states; thus, they are closely spaced.

A. Inter-subband absorption

The inter-subband absorption spectrum is the most relevant quantity in determining the usefulness of self-assembled QWR's for application in IR detection. Fig. 5.4 shows the calculated inter-subband absorption spectra of the self-assembled QWR structure (as depicted in

Fig. 4.1(b)) for three different lengths of period: $L = 72, 50$, and $40a_{[110]}$ (approximately 300 Å, 200 Å, and 160 Å, respectively). In the calculation, we assume that these QWR structures are n-type doped with linear carrier density around $1.2 \times 10^6 \text{ cm}^{-1}$ (which corresponds to a Fermi level around 25 meV above the conduction band minimum).

For comparison purposes, we show results for polarization vector along both the $[110]$ (solid curves) and $[001]$ directions (dashed curves). The results for $[1\bar{1}0]$ polarization are zero due to the strict translational invariance imposed in our model calculation.

The peak positions for the inter-subband transition with normal incidence (for $[110]$ polarization) are around 65 meV, 95 meV, and 125 meV for the three cases considered here. All these are within the desirable range of IR detection. As expected, the transition energy increases as the length of period decreases due to the increased degree of lateral confinement. However, the transition energy will saturate at around 125 meV as we further reduce the length of period, since the bound-to-continuum transition is already reached at $L = 40a_{[110]}$.

The absorption strength for the $[110]$ -polarized peak decreases from 13000 cm^{-1} for $L = 72a_{[110]}$ to 7000 cm^{-1} for $L = 40a_{[110]}$. This is mainly due to the fact that α is inversely proportional to $\hbar\omega$ [see Eq. (5.2)] and the peak becomes more spread out in energy as caused by the increased dispersion in C2 subband for narrower QWR. The inter-subband absorption for the $[001]$ polarization is peaked around 125 meV for all three cases. The excited state involved in this transition is the C3 subband which correspond to the $(n_y, n_z) = (1, 2)$ state. Thus, it has the same physical origin as the inter-subband transition used in typical QWIP structure. Although this peak is not useful for IR detection with normal incidence,

it can be used as the second-color detection if one puts a diffraction grating on the surface as typically done in the fabrication of QWIPs. In this respect, the QWR IR detector (for cases 1 and 2) is unique in that it has two strong narrow-band absorption at two distinct wavelengths, which are also polarization dependent. For case 3, the energy positions for the (1,2) and (2,1) states nearly coincide (both are near the top of the quantum well); thus, the inter-subband absorption spectra for [110] and [001] polarizations are peaked at almost the same position. The absorption strength for the [001]-polarized peak increases from 11000 cm^{-1} for $L = 72a_{[110]}$ to 18000 cm^{-1} for $L = 40a_{[110]}$. This is mainly due to the fact that α is inversely proportional to the cross-sectional area of the QWR.

B. Inter-band absorption

The inter-band optical transitions are important for the characterization of self-assembled QWR's, since they are readily observable via the Photoluminescence (PL) or optical transmission experiment. For IR-detector application, they offer another absorption peak at mid IR wavelengths, which can be used together with the inter-subband transitions occurred at far IR wavelengths for multi-colored detection. Thus, to understand the full capability of the self-assembled QWR material, we also need to analyze the inter-band absorption.

Fig. 5.5 shows the inter-band absorption spectra for SILO QWR's with (a) $L = 72a_{[110]}$, (b) $L = 50a_{[110]}$, and (c) $L = 40a_{[110]}$. Both doped and undoped samples are considered. The results for the undoped samples are denoted by solid (with exciton effect) and dashed (without the exciton effect) curves. The results for doped samples (with $1.2 \times 10^6 \text{cm}^{-1}$) are

indicated by dotted curves. The upper group of curves labeled $(x, y) - pol.$ are for absorption averaged over the x and y polarizations. The lower group labeled $z - pol.$ are for polarization along the z direction. The PL properties of the $L = 72a_{[110]}$ structure with alloy mixing characterized by $x_m = 1.0$ and $b = 33\text{\AA}$ has been studied in our previous paper.³⁴ The QWR structure has a gap around 0.74 eV with a PL polarization ratio ($P_{[1\bar{1}0]}/P_{[110]}$) around 2.2. The absorption coefficient for this structure with excitonic effect has a peak strength around 10^4 cm^{-1} . The binding energy for the ground state exciton (derived primarily from the top valence subband and the lowest conduction subband) is around 20 meV. Thus, the peak position in the absorption spectrum shifts from 0.76 meV (without the excitonic effect) to 0.74 meV (with the excitonic effect). The excitonic effect also enhances the peak strength by about 20%.

For the QWR structures with $L = 50a_{[110]}$ and $L = 40a_{[110]}$, we obtain similar absorption spectra with slightly stronger exciton peaks. The exciton binding is around 30 (40) meV, and the excitonic enhancement factor of the first peak is around 1.35 (1.47) for the $L = 50(40)a_{[110]}$ case. The enhanced peak strength and larger exciton binding energy are caused by the stronger lateral confinement for electrons and holes,. Comparing the dashed curves with the dotted curves, we can see the effect of phase-space filling due to doping. For samples grown for mid-IR detector application with doping levels below $1.2 \times 10^6 \text{ cm}^{-1}$, the absorption spectrum should vary between the undoped case (solid curve) and the heavily doped case (dashed curve) presented here. There is no experiments so far for these structures we designed, and the experiments on these IR detectors are highly desirable.

IV. SUMMARY

We have studied the inter-subband and inter-band absorption spectra for self-assembled InGaAs quantum wires for consideration in IR-detector application. Detailed band structures, microscopic strain distributions, and excitonic effects all have been taken into account. A number of realistic structures grown via strain-induced lateral ordering process are examined. We find that the self-assembled InGaAs quantum wires are good candidate for multi-colored IR detector materials. They offer two groups of strong IR absorption peaks: one in the far-IR range with wavelengths covering 10 - 20 μm (via the inter-subband transition), the other in the mid-IR range with wavelengths shorter than 1.5 μm (via the inter-band transitions). Due to the strain induced lateral modulation, the inter-subband transition is strong for normal incident light with polarization along the direction of lateral modulation ([110]). The absorption strength is around 10^4 cm^{-1} for a doping level of $1.2 \times 10^6 \text{ cm}^{-1}$. This gives the self-assembled InGaAs quantum wires a distinct advantage over the quantum well systems for application in IR detection.

The inter-subband absorption is found to be sensitive to the length of period (L) of lateral modulation with the absorption peak position varying from 60 meV to 120 meV as the length of period is reduced from 300 Å to 160 Å. However, further reduction in the length of period does not shift the absorption peak very much, as the excited states become laterally unconfined.

For the inter-band transition, we find that the excitonic effect enhances the absorption

peak strength by about 20-50 %, and shift the peak position by about 20-50 meV for the undoped structures considered. These results are useful for characterization of the material and for the design of mid-IR photo-detectors. We find that the reduction in the period length (L) leads to stronger lateral confinement, hence larger exciton binding and stronger absorption strength. For the doped samples whose inter-subband transitions are studied, the inter-band transition (without excitonic effect) gives a broad band absorption in the mid-IR range (with wavelengths shorter than $1.5\ \mu m$) with a strength between 4000 and $10000\ \text{cm}^{-1}$. The simultaneous presence of this mid-IR absorption and the narrow band far-IR absorption near $10\ \mu m$ provide a unique combination for multi-color IR detection application.

In conclusion, we have successfully demonstrated that self-assembled quantum wires are promising IR-detector materials and we have provided theoretical modeling for the optical characteristics of realistic QWR structures, which can be used to guide future fabrication of quantum wire infrared detectors.

REFERENCES

- ¹ B. F. Levine, J. Appl. Phys., vol. 74, pp. R1-R81, 1993, and references therein.
- ² H. C. Liu, B. F. Levine, and J. Y. Anderson, *Quantum Well Intersubband Transition Physics and Devices*, (Kluwer, Dordrecht, Netherlands, 1994).
- ³ M. Z. Tidrow and K. Bacher, Appl. Phys. Lett., vol. 69, pp. 3396-3398, 1996.
- ⁴ S. Maimon, G. M. Cohen, E. Finkman, G. Bahir, S. E. Schachman, and D. Ritter, Appl. Phys. Lett., vol. 73, pp. 800-802, 1998.
- ⁵ E. Kapon, S. Simhony, J. P. Harbison, L. T. Florez, and P. Worland, Appl. Phys. Lett., vol. 56, pp. 1825-1827, 1990.
- ⁶ M. Tsuchiya, J.M. Gaines, R.H. Yan, R.J. Simes, P.O. Holtz, L.A. Coldren, and P.M. Petroff, Phys. Rev. Lett., Vol. 62, pp. 466-469, 1989.
- ⁷ S. Hasegawa, M. Sato, K. Maehashi, H. Asahi, and H. Nakashima, J. Crystal Growth, Vol. 111, pp. 371-375 1991.
- ⁸ R. Notzel and K. Ploog, J. Vac. Sci. Technol. A, Vol. 10, pp. 617-622, 1992.
- ⁹ Y. Miyake, H. Hirayama, K. Kudo, S. Tamura, s. Arai, M. Asada, Y. Miyamoto, and Y. Suematsu, J. Quantum electron., vol. QE-29, pp. 2123-2131, 1993.
- ¹⁰ S.J. Kim, H. Asahi, M. Takemoto, K. Asami, M. Takeuchi, and S. Gonda, Jpn. J. Appl. Phys., Vol. 35, pp. 4225-4231, 1996.

- ¹¹ Y. Tang, H. T. Lin, D. H. Rich, P. Colter, and S. M. Vernon, Phys. Rev. B, vol. 53, pp. R10501-10504, 1996.
- ¹² S. T. Chou, K. Y. Cheng, L. J. Chou, and K. C. Hsieh, Appl. Phys. Lett., vol. 17, 2220, 1995; J. Appl. Phys., vol. 78, pp. 6270-6275, 1995; J. Vac. Sci. Technol. B, vol. 13, pp. 650-652, 1995; K. Y. Cheng, K. C. Hsien, and J. N. Baillargeon, Appl. Phys. Lett., vol. 60, pp. 2892-2894, 1992.
- ¹³ D. E. Wohlert, S. T. Chou, A. C. Chen, K. Y. Cheng, and K. C. Hsieh, Appl. Phys. Lett., vol. 17, pp. 2386-2388, 1996.
- ¹⁴ K. Y. Cheng, Proceedings of the twenty-seventh state-of-the-art program on compound semiconductors (*SOTOPCOCSXXVII*). Electrochem. Soc. 1997, pp. 154-160. Pennington, NJ, USA.
- ¹⁵ D.E. Wohlert, S. T. Chou and K. Y. Cheng, J. Crystal growth, Vol. 175-176, pp. 1162-1166, 1997.
- ¹⁶ A. M. Moy, G. W. Pickrell, K. Y. Cheng, J. Vac. Sci. Technol. B, Vol. 16, pp. 1347-1351, 1998.
- ¹⁷ S. T. Chou, D. E. Wohlert, K. Y. Cheng, and K. C. Hsieh, J. Appl. Phys., vol. 83, pp. 3469-3472, 1998.
- ¹⁸ D.E. Wohlert, and K. Y. Cheng, Appl. Phys. Lett., vol. 76, pp. 2247-2249, 2000.
- ¹⁹ D. J. Eaglesham and M.Cerullo, Phy. Rev. Lett., vol. 64, pp. 1943-1946, 1990.

- ²⁰ G. S. Solomon, J. A. Trezza, A. F. Marshall, and J. S. Harris, Jr., Phys. Rev. Lett., vol. 76, pp. 952-955, 1996.
- ²¹ I. Mukhametzhanov, Z. Wei, R. Heitz, and A. Madhukar, Appl. Phys. Lett., vol. 75, pp. 85-87, 1999.
- ²² M. Grundmann, O. Stier, and D. Bimberg, Phys. Rev. B, vol. 52, pp. 11969-11981, 1995.
- ²³ O. Stier, M. Grundmann, and D. Bimberg, Phys. Rev. B, vol. 59, pp. 5688-5701, 1999.
- ²⁴ D.E. Wohlert, and K. Y. Cheng, private communications.
- ²⁵ Y. C. Chang, Phys. Rev. B, vol. 37, pp. 8215-8222, 1988.
- ²⁶ P. N. Keating, Phys. Rev., vol. 145, pp. 637-645, 1966.
- ²⁷ R. M. Martin, Phys. Rev. B, vol. 1, pp. 4005-4011, 1969.
- ²⁸ H. Jiang and J. Singh, Phys. Rev. B, vol. 56, pp. 4696-4701, 1997.
- ²⁹ R. J. Keyes, *Optical and infrared Detectors*, (Springer-Verlag, New York, 1980).
- ³⁰ M. P. Houngh and Y. C. Chang, J. Appl. Phys., vol. 65, pp. 3096-3098, 1989.
- ³¹ D. S. Citrin and Y. C. Chang, Phys. Rev. B, vol. 43, pp. 11703-11719, 1991.
- ³² S. Sun and Y. C. Chang, Phys. Rev. B, vol. 62, pp. 13631-13640, 2000.
- ³³ L. X. Li and Y. C. Chang, J. Appl. Phys., vol. 84, pp. 6162-6169, 1998.
- ³⁴ L. X. Li, S. Sun, and Y. C. Chang, J. Appl. Phys., vol. 89, pp. 2251-2260, 2001.

³⁵ E. O. Kane, J. Phys. Chem. Solids, vol. 1, pp. 82-99, 1956.

³⁶ L. X. Li, S. Sun, and Y. C. Chang, submitted for publication. 2001.

FIGURES

FIG. 1. Conduction band and valence band edges for self-assembled QWR structure depicted in Fig. 1 for (a) $L = 50a_{[110]}$ and (b) $L = 40a_{[110]}$. Dashed: without alloy mixing. Solid: with alloy mixing described by $x_m = 1.0$ and $b = 8a_{[110]}$.

FIG. 2. Conduction subband structure of self-assembled QWR for (a) $L = 50a_{[110]}$ and (b) $L = 40a_{[110]}$ with $x_m = 1.0$ and $b = 8a_{[110]}$.

FIG. 3. Valence subband structure of self-assembled QWR for (a) $L = 50a_{[110]}$ and (b) $L = 40a_{[110]}$ with $x_m = 1.0$ and $b = 8a_{[110]}$.

FIG. 4. Inter-subband absorption spectra of self-assembled QWR for (a) $L = 72a_{[110]}$, (b) $L = 50a_{[110]}$, and (c) $L = 40a_{[110]}$ with $x_m = 1.0$ and $b = 8a_{[110]}$. Solid: $[110]$ polarization, dashed : $[001]$ polarization.

FIG. 5. Inter-band absorption spectra of self-assembled QWR's for (a) $L = 72a_{[110]}$, (b) $L = 50a_{[110]}$, and (c) $L = 40a_{[110]}$ with $x_m = 1.0$ and $b = 8a_{[110]}$. Solid: undoped sample with excitonic effect. Dashed: undoped sample without excitonic effect. Dotted : doped sample without excitonic effect. The set of curves with larger strength are for unpolarized light with normal incidence. The set of curves with smaller strength are for $[001]$ polarization.

6. SUMMARY

In this thesis, we have studied theoretically the electronic, optical properties and microstrain profiles of SILO quantum wires.

In our virtual crystal approximation model of strain, we considered the combination of two bi-axial strains, one in the (001) plane (due to the lattice mismatch at the interfaces between GaInAs and AlGaInAs) and the other in the (110) plane (due to the Ga composition modulation). The resulting strains in the QW layers consist of both hydrostatic and uniaxial components. The band structures and optical matrix elements are then calculated by incorporating the strain deformation potential into our total Hamiltonian for the SILO wires. This model predicts that both electron and holes are confined in the Ga-rich region and optical anisotropy is in agreement with that observed experimentally. We find that the biaxial strain due to the lattice mismatch between the Ga-rich and In-rich regions is most dominant. It tends to increase the lateral confinement in the QWR and enhances the anisotropy of the optical transitions which may be useful for certain applications in optical

communication. We also calculated the effect of lateral composition modulation on the band structures and optical properties and find that it increases the band gaps and reduces the optical anisotropy.

Although this method can explain the band gaps and anisotropy of the experiments, it lacks of predicting power to future design of desired bands and optics due to the fact that it ignored the actual SPS structures of the growth.

As it is shown in our atomistic model the detailed atomistic strain have remarkable influences on the optical anisotropy.

In our atomistic strain model, the actual SPS structure and the microscopic strain distribution have been taken into account. The effects of microscopic strain distribution on the valence subband structures and optical matrix elements are studied for two types of self-assembled QWR structures, one with (2/2) SPS structure and the other with (2/2.25) SPS structure, with varying degrees of lateral alloy mixing. The clamping effect due to the applying layer is also examined. The VFF model is used to calculate the equilibrium atomic positions in the QWR model structures. This allows the calculation of the

strain distribution at the atomistic level.

We find that in model structures with thick capping layer (clamped case), the magnitude of shear strain is quite large, around 2%, when the lateral alloy mixing is absent, and it reduces substantially when the lateral alloy mixing is introduced. We found that the shear strain effect can alter the valence subband structures substantially when the holes are confined in the Ga-rich region, and it gives rise to a reversed optical anisotropy compared with QWR structures with negligible shear strain. For the unclamped case, the anisotropy is always in favor of polarization along the wire regardless of the degree of lateral alloy mixing due to the fact that the effect of shear strain is less dramatic when the holes and electrons are confined in the In-rich region. The band gap and polarization ratio obtained for unclamped SPS structures are consistent with experimental observations on most self-assembled InGaAs QWRs with similar specifications. For clamped (2/2) SPS structure without a mixing, we predicted a reversed optical anisotropy compared with the PL measurements for most InAs/GaAs self-assembled QWRs (which are usually grown with thin capping layers). However, there exist a

InAs/GaAs self-assembled QWR samples which display the reversed optical anisotropy at 77 K, and recent experimental studies also indicated a reversed optical anisotropy in many samples at 300 K. Our studies demonstrated a possibility for the reversed optical anisotropy that is due to the shear strain effect. Those results should be verified in the future SILO experiments. In particular, one can apply external stress to convert the unclamped case into the clamped case, and it would be interesting to see that the clamping effect will reverse the optical anisotropy. There may be other possibilities for the reversed optical anisotropy at 300K. For example, the thermal population of the excited hole states, which have different atomic characters from the lowest-lying hole states as may also lead to a change in the polarization ratio.

We also studied the effects of the exciton on the optical absorption spectra. We found that the exciton in the SILO wires enhanced the absorption amplitude by 1.2-1.5 times. The polarization spectrum are also studied for intersubbands. It is found that the intersubband absorption is sensitive to the length of period of lateral modulation which is successfully used to engineer the peak position for the purpose of IR detection. For the calculation of

intersubband transitions, we have not considered the correlation effect due to electron-electron interaction. For low-dimensional systems such as quantum wires or quantum dots, the correlation effect may play an important role. Especially in the modeling of dark current and photocurrent for IR detection, the correlation effect may lead to interesting phenomenon such as the Coulomb blockade[1] or Kondo effect[3].

For the future studies, the mechanisms that caused the temperature insensitivity of SILO wires need to be investigated and explained. So far, there is no good explanation for the experimental results on the temperature stability. Our initial guess is that: the multi-axial strain slowed down the gap's dependence on the volume thermal expansion, also the effects of electron-phonon coupling on the band gap for the strained and confined one dimension quantum wires are weaker. Together, this two effects's combination will lead to the super stability and even blue shift of the gap with the temperature.

Quantum dots(QDs) represent another dimension for us to extend our work. Due to its possible application on the detectors, memory devices, and laser instruments, QD is attracting a lot of attention recently. Our methods

could easily and are being extended to the quantum dots.

For the quantum dot array, the interplay of quantum confinement, interdot tunneling, and strong intradot Coulomb interactions leads to many interesting physical phenomena. As the interdot tunneling strength varies, different phases corresponding to isolated Coulomb blockade, collective Coulomb blockade, and vanishing Coulomb blockade will emerge[1]. Also increasing interdot tunnelling could lead to the transition from discrete energy levels into mini-band formation[2]. For doped systems, this will lead to a insulator-metal transition[1,2]. On the other hand, the Kondo correlation of the unpaired localized electron and delocalized electron will lead to further interesting physics in the quantum dot system[3].

It is natural this method will provide the powerful guidance to the design of the novel QD structure and interesting physics.

REFERENCES

- ¹ C.A. Stafford, and S. Das Sarma, Phys.Rev.Lett **72**, 3590(1994)
- ² T. Inoshita, A.Shimizu, Y. Kuramoto and H. Sakaki, Phys.Rev.B **48**,
14725(1993)
- ³ D. G. Gordon, H. Shtrikman, D. Mahalu, d. Abusch-Mager, U. Meirav and
M.A. Kastner, Nature,**391**, 156(1998)